

**PART NUMBER****MC28F008-10-ROC****Rochester Electronics****Manufactured Components**

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**Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
  - Class Q Military
  - Class V Space Level

**Qualified Suppliers List of Distributors (QSLD)**

- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

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## VS28F016SV, MS28F016SV FlashFile™ MEMORY

- **VS28F016SV**
  - -40°C to +125°C
  - SE2 Grade
- **MS28F016SV**
  - -55°C to +125°C
  - QML Certified
  - SE1 Grade
- **SmartVoltage Technology**
  - User-Selectable 3.3V or 5V V<sub>CC</sub>
  - User-Selectable 5V or 12V V<sub>PP</sub>
- **Three Voltage/Speed Options**
  - 80 ns Access Time, 5.0V ± 5%
  - 85 ns Access Time, 5.0V ± 10%
  - 120 ns Access Time, 3.3V ± 10%
- **1 Million Erase Cycles per Block Typical**
- **14.3 MB/sec Burst Write Transfer Rate**
- **Configurable x8 or x16 Operation**
- **56-Lead, 0.8mm x 13.5mm SSOP Plastic Package**
- **Backwards-Compatible with VE28F008, M28F008 and 28F016SA Command Set**
- **Revolutionary Architecture**
  - Multiple Command Execution
  - Write During Erase
  - Command Super-Set of the Intel VE28F008, M28F008
  - Page Buffer Write
- **Multiple Power Savings Modes**
- **Two 256-Byte Page Buffers**
- **State-of-the-Art 0.6 μm ETOX™ IV Flash Technology**

Intel's VS/MS28F016SV, 16-Mbit FlashFile™ Memory is the latest member of Intel's high density, high performance memory family for the Industrial, Special Environment, and Military markets. Its user selectable V<sub>CC</sub> and V<sub>PP</sub> (SmartVoltage Technology), innovative capabilities, 100% compatibility with the VE28F008 and M28F008, multiple power savings modes, selective block locking, and very fast read/write performance make it the ideal choice for any applications that need a high density and a wide temperature range memory device. The VS/MS28F016SV is the ideal choice for designers who need to break free from the dependence on slow rotating media or battery backed up memory arrays.

With two product grades (SE1: -55°C to +125°C, and SE2: -40°C to +125°C) available, the VS/MS28F016SV is perfect for the non-PC industries like Telecommunications, Embedded/Industrial, Automotive, Navigation, Wireless Communication, Commercial Aircraft, and all Military programs.

The VS/MS28F016SV's x8/x16 architecture allows for the optimization of the memory to processor interface. The flexible block locking options enable bundling of executable application software in a Resident Flash Array (RFA), PCMCIA Memory or ATA Cards or Memory modules.

The VS/MS28F016SV is offered in a 56-lead SSOP (Shrink Small Outline Package) and is manufactured on Intel's 0.6 μm ETOX™ IV process technology.

# VS28F016SV, MS28F016SV FlashFile™ MEMORY

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## 1.0 INTRODUCTION

The documentation of the Intel VS/MS28F016SV memory device includes this data sheet, a detailed user's manual, and a number of application notes, all of which are referenced at the end of this data sheet.

The data sheet is intended to give an overview of the chip feature-set and of the operating AC/DC specifications. The 28F016SA (compatible with VS/MS28F016SV) User's Manual provides complete descriptions of the user modes, system interface examples and detailed descriptions of all principles of operation. It also contains the full list of software algorithm flowcharts, and a brief section on compatibility with the Intel VE28F008 and M28F008.

## 1.1 Enhanced Features

The VS/MS28F016SV is backwards compatible with the VE28F008 and M28F008 and offers the following enhancements:

- SmartVoltage Technology
  - Selectable 5.0V or 12.0V  $V_{pp}$
- $V_{pp}$  Level Bit in Block Status Register
- Internal 3/5V Detection Circuitry
- Additional RY/BY# Configuration
  - Pulse-On-Write/Erase
- Additional Upload Device Information Command Feedback
  - Device Revision Number
  - Device Proliferation Code
  - Device Configuration Code
- x8/x16 Architecture
- Improved Read/Write Performance
- Block Locking
- Simplified Processor Interface
- 2 Page Buffers
- Instruction Queuing

## 1.2 Product Overview

The VS/MS28F016SV is a high-performance, 16-Mbit (16,777,216-bit) block erasable, non-volatile random access memory, organized as either 1 Mword x 16 or 2 Mbyte x 8. The VS/MS28F016SV includes thirty-two 64-KB (65,536 byte) blocks or thirty-two 32-KW (32,768 word) blocks. A chip memory map is shown in Figure 3.

The implementation of a new architecture, with many enhanced features, will improve the device operating characteristics and result in greater product reliability and ease of use.

The VS/MS28F016SV incorporates SmartVoltage technology, providing  $V_{CC}$  operation at both 3.3V and 5.0V and program and erase capability at  $V_{pp} = 12.0V$  or 5.0V. Operating at  $V_{CC} = 3.3V$ , the VS/MS28F016SV consumes approximately one-half the power consumption at 5.0V  $V_{CC}$ , while 5.0V  $V_{CC}$  provides highest read performance capability.  $V_{pp} = 5.0V$  operation eliminates the need for a separate 12.0V converter, while  $V_{pp} = 12.0V$  maximizes write/erase performance. In addition to the flexible program and erase voltages, the dedicated  $V_{pp}$  gives complete code protection with  $V_{pp} \leq V_{PPLK}$ .

Depending on system design specifications, the VS/MS28F016SV is capable of supporting

- 80 ns access times with a  $V_{CC}$  of 5.0V  $\pm 5\%$  and loading of 30 pF
- 85 ns access times with a  $V_{CC}$  of 5.0V  $\pm 10\%$  and loading of 100 pF
- 120 ns access times with a  $V_{CC}$  of 3.3V  $\pm 10\%$  and loading of 50 pF

Internal 3.3V or 5.0V  $V_{CC}$  detection automatically configures the device internally for optimized 3.3V or 5.0V Read/Write operation.

A Command User Interface (CUI) serves as the system interface between the microprocessor or micro-controller and the internal memory operation.

Internal Algorithm Automation allows Byte/Word Writes and Block Erase operations to be executed using a Two-Write command sequence to the CUI in the same way as the VE28F008 or M28F008 8-Mbit FlashFile memory.

A super-set of commands has been added to the basic VE28F008 or M28F008 command-set to achieve higher write performance and provide additional capabilities. These new commands and features include:

- Page Buffer Writes to Flash
- Command Queuing Capability
- Automatic Data Writes during Erase
- Software Locking of Memory Blocks
- Two-Byte Successive Writes in 8-bit Systems
- Erase All Unlocked Blocks

Writing of memory data is performed in either byte or word increments, typically within 6  $\mu$ sec (12.0V Vpp) — a 33% improvement over the VE28F008 or M28F008. A Block Erase operation erases one of the 32 blocks in typically 0.6 sec (12.0V Vpp), independent of the other blocks, which is about a 65% improvement over the VE28F008 or M28F008.

Each block can be written and erased a minimum of 100,000 cycles. Systems can achieve one million Block Erase Cycles by providing wear-leveling algorithms and graceful block retirement. These techniques have already been employed in many flash file systems and hard disk drive designs.

The VS/MS28F016SV incorporates two Page Buffers of 256 bytes (128 words) each to allow page data writes. This feature can improve a system write performance by up to 4.8 times over previous flash memory devices, which have no Page Buffers.

All operations are started by a sequence of Write commands to the device. Three Status Registers (described in detail later in this data sheet) and a RY/BY# output pin provide information on the progress of the requested operation.

While the VE28F008 or M28F008 requires an operation to complete before the next operation can be requested, the VS/MS28F016SV allows queuing of the next operation while the memory executes the current operation. This eliminates system overhead when writing several bytes in a row to the array or erasing several blocks at the same time. The VS/MS28F016SV can also perform Write operations to one block of memory while performing Erase of another block.

The VS/MS28F016SV provides selectable block locking to protect code or data such as Device Drivers, PCMCIA card information, ROM-Executable O/S or Application Code. Each block has an associated non-volatile lock-bit which determines the lock status of the block. In addition, the VS/MS28F016SV has a master Write Protect pin (WP#) which prevents any modifications to memory blocks whose lock-bits are set.

The VS/MS28F016SV contains three types of Status Registers to accomplish various functions:

- A Compatible Status Register (CSR) which is 100% compatible with the VE28F008 or M28F008 FlashFile memory Status Register. The CSR, when used alone, provides a straightforward upgrade capability to the VS/MS28F016SV from a VE28F008- or M28F008-based design.

- A Global Status Register (GSR) which informs the system of command Queue status, Page Buffer status, and overall Write State Machine (WSM) status.
- 32 Block Status Registers (BSRs) which provide block-specific status information such as the block lock-bit status.

The GSR and BSR memory maps for Byte-Wide and Word-Wide modes are shown in Figures 4 and 5.

The VS/MS28F016SV incorporates an open drain RY/BY# output pin. This feature allows the user to OR-tie many RY/BY# pins together in a multiple memory configuration such as a Resident Flash Array.

Other configurations of the RY/BY# pin are enabled via special CUI commands and are described in detail in the 28F016SA User's Manual.

The VS/MS28F016SV's Upload Device Information command is enhanced compared to the VE28F008 or M28F008, providing access to additional device information. This command uploads the Device Revision Number, Device Proliferation Code and Device Configuration Code. The Device Proliferation Code for the VS/MS28F016SV is 01H, and the Device Configuration Code identifies the current RY/BY# configuration. Section 4.4 documents the exact page buffer address locations for all uploaded information. A subsequent Page Buffer Swap and Page Buffer Read command sequence is necessary to read the correct device information.

The VS/MS28F016SV also incorporates a dual chip-enable function with two input pins, CE<sub>0</sub># and CE<sub>1</sub>#. These pins have exactly the same functionality as the regular chip-enable pin, CE#, on the VE28F008 or M28F008. For minimum chip designs, CE<sub>1</sub># may be tied to ground and use CE<sub>0</sub># as the chip enable input. The VS/MS28F016SV uses the logical combination of these two signals to enable or disable the entire chip. Both CE<sub>0</sub># and CE<sub>1</sub># must be active low to enable the device. If either one becomes inactive, the chip will be disabled. This feature, along with the open drain RY/BY# pin, allows the system designer to reduce the number of control pins used in a large array of 16-Mbit devices.

The BYTE# pin allows either x8 or x16 read/writes to the VS/MS28F016SV. BYTE# at logic low selects 8-bit mode with address A<sub>0</sub> selecting between low byte and high byte. On the other hand, BYTE#



at logic high enables 16-bit operation with address  $A_1$  becoming the lowest order address and address  $A_0$  is not used (don't care). A device block diagram is shown in Figure 1.

The VS/MS28F016SV is specified for a maximum access time of 80 ns ( $t_{ACC}$ ) at 5.0V operation (4.75V to 5.25V) in either the SE1 or SE2 grades. A corresponding maximum access time of 120 ns at 3.3V (3.0V to 3.6V) is achieved for reduced power consumption applications.

The VS/MS28F016SV incorporates an Automatic Power Saving (APS) feature which substantially reduces the active current when the device is in static mode of operation (addresses not switching). In APS mode, the typical  $I_{CC}$  current is 1 mA at 5.0V (0.8 mA at 3.3V).

A deep power-down mode of operation is invoked when the  $RP\#$  (called  $PWD\#$  on the VE28F008 or M28F008) pin transitions low. This mode brings the

device power consumption to less than 30.0  $\mu A$ , typically, and provides additional write protection by acting as a device reset pin during power transitions. A reset time of 500 ns (5.0V  $V_{CC}$  operation) is required from  $RP\#$  switching high until outputs are again valid. In the Deep Power-Down state, the WSM is reset (any current operation will abort) and the CSR, GSR and BSR registers are cleared.

A CMOS standby mode of operation is enabled when either  $CE_0\#$  or  $CE_1\#$  transitions high and  $RP\#$  stays high with all input control pins at CMOS levels. In this mode, the device typically draws an  $I_{CC}$  standby current of 70  $\mu A$  at 5V  $V_{CC}$ .

## 2.0 DEVICE PINOUT

The VS/MS28F016SV 56L-SSOP pinout configuration is shown in Figure 2.

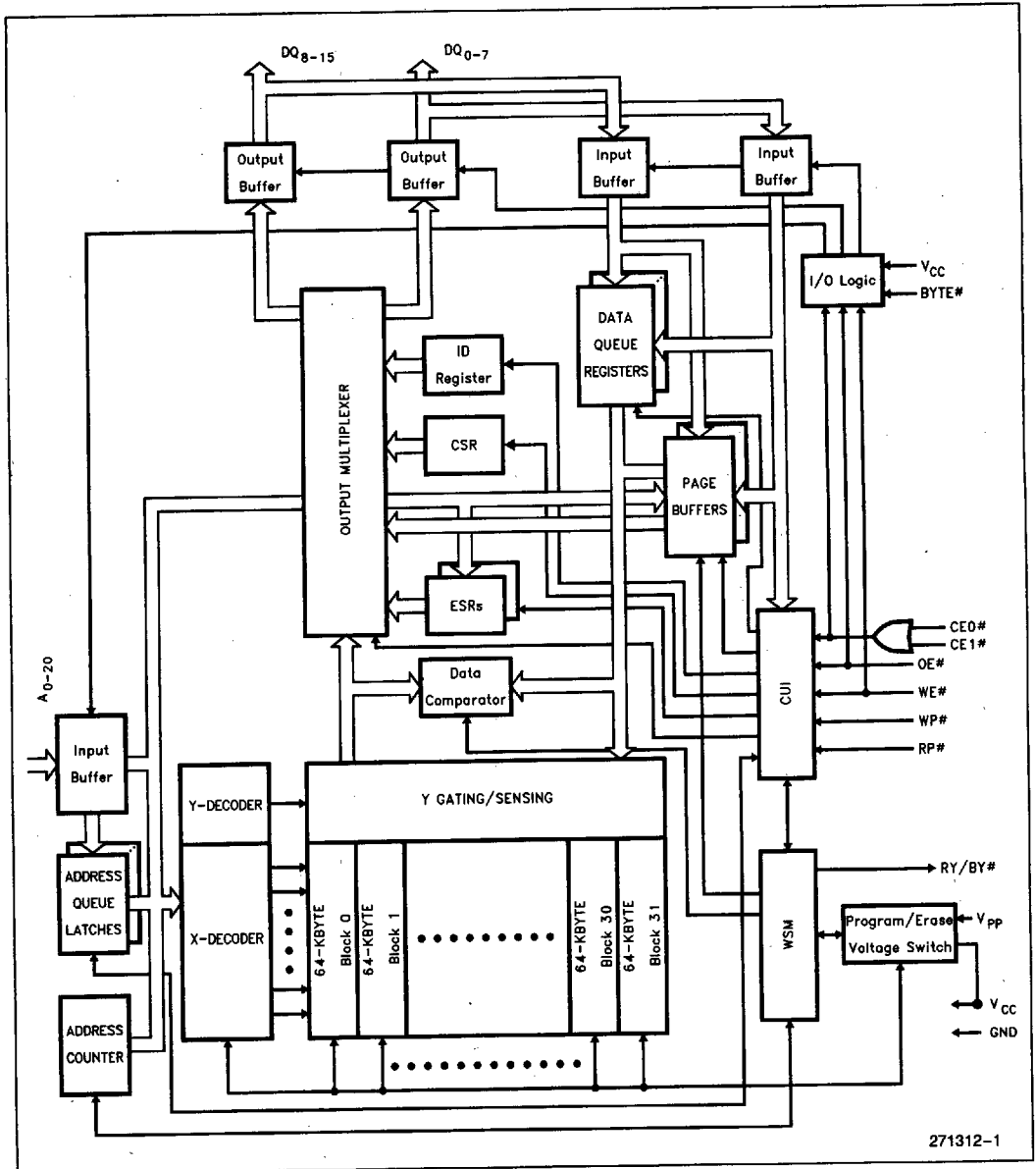


Figure 1. Block Diagram

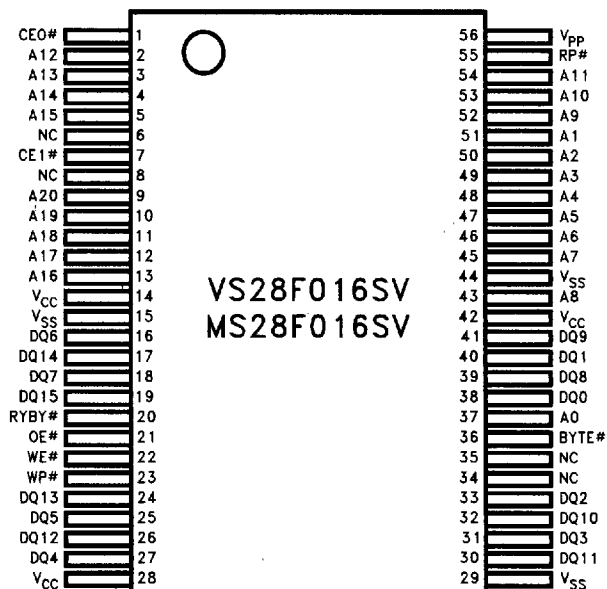
## 2.1 Lead Descriptions

Symbol	Type	Name and Function
A <sub>0</sub>	INPUT	<b>BYTE-SELECT ADDRESS:</b> Selects between high and low byte when device is in x8 mode. This address is latched in x8 Data Writes. Not used in x16 mode (i.e., the A <sub>0</sub> input buffer is turned off when BYTE # is high).
A <sub>1</sub> - A <sub>15</sub>	INPUT	<b>WORD-SELECT ADDRESSES:</b> Select a word within one 64-Kbyte block. A <sub>6-15</sub> selects 1 of 1024 rows, and A <sub>1-5</sub> selects 16 of 512 columns. These addresses are latched during Data Writes.
A <sub>16</sub> - A <sub>20</sub>	INPUT	<b>BLOCK-SELECT ADDRESSES:</b> Select 1 of 32 Erase blocks. These addresses are latched during Data Writes, Erase and Lock-Block operations.
DQ <sub>0</sub> - DQ <sub>7</sub>	INPUT/OUTPUT	<b>LOW-BYTE DATA BUS:</b> Inputs data and commands during CUI write cycles. Outputs array, buffer, identifier or status data in the appropriate read mode. Floated when the chip is de-selected or the outputs are disabled.
DQ <sub>8</sub> - DQ <sub>15</sub>	INPUT/OUTPUT	<b>HIGH-BYTE DATA BUS:</b> Inputs data during x16 Data-Write operations. Outputs array, buffer or identifier data in the appropriate read mode; not used for Status Register reads. Floated when the chip is de-selected or the outputs are disabled.
CE <sub>0</sub> #, CE <sub>1</sub> #	INPUT	<b>CHIP ENABLE INPUTS:</b> Activate the device's control logic, input buffers, decoders and sense amplifiers. With either CE <sub>0</sub> # or CE <sub>1</sub> # high, the device is de-selected and power consumption reduces to standby levels upon completion of any current Data-Write or Erase operations. Both CE <sub>0</sub> #, CE <sub>1</sub> # must be low to select the device. All timing specifications are the same for both signals. Device Selection occurs with the latter falling edge of CE <sub>0</sub> # or CE <sub>1</sub> #. The first rising edge of CE <sub>0</sub> # or CE <sub>1</sub> # disables the device.
RP #	INPUT	<b>RESET/POWER-DOWN:</b> RP # low places the device in a Deep Power-Down state. All circuits that burn static power, even those circuits enabled in standby mode, are turned off. When returning from Deep Power-Down, a recovery time of 500 ns at 5.0V V <sub>CC</sub> is required to allow these circuits to power-up. When RP # goes low, any current or pending WSM operation(s) are terminated, and the device is reset. All Status Registers return to ready (with all status flags cleared). Exit from Deep Power-Down places the device in read array mode.
OE #	INPUT	<b>OUTPUT ENABLE:</b> Gates device data through the output buffers when low. The outputs float to tri-state off when OE # is high. <b>NOTE:</b> CE <sub>x</sub> # overrides OE #, and OE # overrides WE #.
WE #	INPUT	<b>WRITE ENABLE:</b> Controls access to the CUI, Page Buffers, Data Queue Registers and Address Queue Latches. WE # is active low, and latches both address and data (command or array) on its rising edge. Page Buffer addresses are latched on the falling edge of WE #.



## 2.1 Lead Descriptions (Continued)

Symbol	Type	Name and Function
RY/BY#	OPEN DRAIN OUTPUT	<b>READY/BUSY:</b> Indicates status of the internal WSM. When low, it indicates that the WSM is busy performing an operation. RY/BY# high indicates that the WSM is ready for new operations (or WSM has completed all pending operations), or Erase is Suspended, or the device is in deep power-down mode. This output is always active (i.e., not floated to tri-state off when OE# or CE <sub>0</sub> #, CE <sub>1</sub> # are high), except if a RY/BY# Pin Disable command is issued.
WP#	INPUT	<b>WRITE PROTECT:</b> Erase blocks can be locked by writing a non-volatile lock-bit for each block. When WP# is low, those locked blocks as reflected by the Block-Lock Status bits (BSR.6), are protected from inadvertent Data Writes or Erases. When WP# is high, all blocks can be written or erased regardless of the state of the lock-bits. The WP# input buffer is disabled when RP# transitions low (deep power-down mode).
BYTE#	INPUT	<b>BYTE ENABLE:</b> BYTE# low places device in x8 mode. All data is then input or output on DQ <sub>0-7</sub> , and DQ <sub>8-15</sub> float. Address A <sub>0</sub> selects between the high and low byte. BYTE# high places the device in x16 mode, and turns off the A <sub>0</sub> input buffer. Address A <sub>1</sub> , then becomes the lowest order address.
V <sub>PP</sub>	SUPPLY	<b>WRITE/ERASE POWER SUPPLY (12.0V ± 0.6V, 5.0V ± 0.5V):</b> For erasing memory array blocks or writing words/bytes/pages into the flash array. Connection to 12.0V ± 0.6V maximizes Write/Erase Performance. Write and Erase attempts are inhibited with V <sub>PP</sub> at or below 2.0V. <b>NOTE:</b> Write and Erase attempts with V <sub>PP</sub> between 2.0V and 4.5V, between 5.5V and 11.4V, and above 12.6V produce spurious results and should not be attempted.
V <sub>CC</sub>	SUPPLY	<b>DEVICE POWER SUPPLY (3.3V ± 0.3V, 5.0V ± 0.5V; 5.0V ± 0.25V):</b> Internal detection configures the device for 3.3V or 5.0V operation. To switch 3.3V to 5.0V (or vice versa), first ramp V <sub>CC</sub> down to GND (0 Volts), and then power to the new V <sub>CC</sub> voltage. Do not leave any power pins floating.
GND	SUPPLY	<b>GROUND FOR ALL INTERNAL CIRCUITRY:</b> Do not leave any ground pins floating.
NC		<b>NO CONNECT:</b> No internal connection to die, lead may be driven or left floating.



271312-2

24mm x 13.5mm 0.8mm Lead Pitch

Top View

**NOTE:**

56-Lead SSOP Mechanical Diagrams and dimensions are shown at the end of this data sheet.

**Figure 2. SSOP Pinout Configuration**

## 3.0 MEMORY MAPS

A <sub>(20-0)</sub>		A <sub>(20-1)</sub>	
1FFFFF	64-Kbyte Block 31	FFFFF	32-Kword Block 31
1F0000	64-Kbyte Block 30	F8000	32-Kword Block 30
1EFFFF		F7FFF	
1E0000	64-Kbyte Block 29	F0000	32-Kword Block 29
1DFFFF		EF000	
1D0000	64-Kbyte Block 28	E8000	32-Kword Block 28
1CFFFF		E7FFF	
1C0000	64-Kbyte Block 27	E0000	32-Kword Block 27
1BFFFF		D8000	
1B0000	64-Kbyte Block 26	D7FFF	32-Kword Block 26
1AFFFF		D0000	
1A0000	64-Kbyte Block 25	CF000	32-Kword Block 25
19FFFF		C8000	
190000	64-Kbyte Block 24	C7FFF	32-Kword Block 24
18FFFF		C0000	
180000	64-Kbyte Block 23	BFFFF	32-Kword Block 23
17FFFF		B8000	
170000	64-Kbyte Block 22	B7FFF	32-Kword Block 22
16FFFF		B0000	
160000	64-Kbyte Block 21	AFFFF	32-Kword Block 21
15FFFF		A8000	
150000	64-Kbyte Block 20	A7FFF	32-Kword Block 20
14FFFF		A0000	
140000	64-Kbyte Block 19	9FFFF	32-Kword Block 19
13FFFF		98000	
130000	64-Kbyte Block 18	97FFF	32-Kword Block 18
12FFFF		90000	
120000	64-Kbyte Block 17	8FFFF	32-Kword Block 17
11FFFF		88000	
110000	64-Kbyte Block 16	87FFF	32-Kword Block 16
10FFFF		80000	
100000	64-Kbyte Block 15	7FFFF	32-Kword Block 15
0FFFFF		78000	
0F0000	64-Kbyte Block 14	77FFF	32-Kword Block 14
0EFFFF		70000	
0E0000	64-Kbyte Block 13	6FFFF	32-Kword Block 13
0DFFFF		68000	
0D0000	64-Kbyte Block 12	67FFF	32-Kword Block 12
0CFFFF		60000	
0C0000	64-Kbyte Block 11	5FFFF	32-Kword Block 11
0BFFFF		58000	
0B0000	64-Kbyte Block 10	57FFF	32-Kword Block 10
0AFFFF		50000	
0A0000	64-Kbyte Block 9	4FFFF	32-Kword Block 9
09FFFF		48000	
090000	64-Kbyte Block 8	47FFF	32-Kword Block 8
08FFFF		40000	
080000	64-Kbyte Block 7	3FFFF	32-Kword Block 7
07FFFF		38000	
070000	64-Kbyte Block 6	37FFF	32-Kword Block 6
06FFFF		30000	
060000	64-Kbyte Block 5	2FFFF	32-Kword Block 5
05FFFF		28000	
050000	64-Kbyte Block 4	27FFF	32-Kword Block 4
04FFFF		20000	
040000	64-Kbyte Block 3	1FFFF	32-Kword Block 3
03FFFF		18000	
030000	64-Kbyte Block 2	17FFF	32-Kword Block 2
02FFFF		10000	
020000	64-Kbyte Block 1	0FFFF	32-Kword Block 1
01FFFF		08000	
010000	64-Kbyte Block 0	07FFF	32-Kword Block 0
00FFFF		00000	
000000			

Byte-Wide (x8) Mode

Word-Wide (x16) Mode

271312-3

Figure 3. VS/MS28F016SV Memory Maps (Byte-Wide and Word-Wide Modes)

### 3.1 Extended Status Registers Memory Map

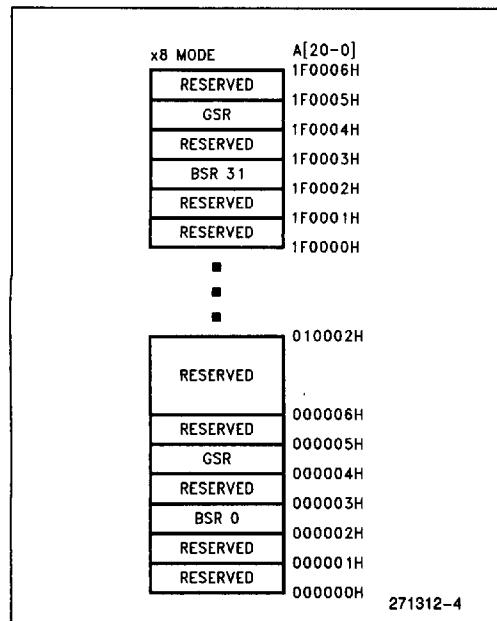


Figure 4. Extended Status Register Memory Map (Byte-Wide Mode)

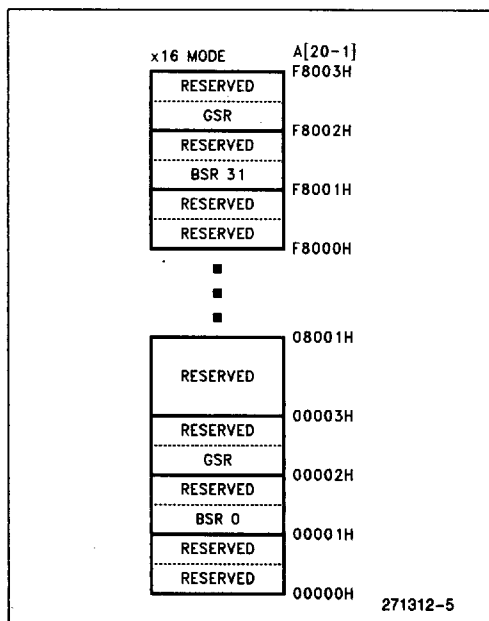


Figure 5. Extended Status Register Memory Map (Word-Wide Mode)

## 4.0 BUS OPERATIONS, COMMANDS AND STATUS REGISTER DEFINITIONS

### 4.1 Bus Operations for Word-Wide Mode (BYTE# = V<sub>IH</sub>)

Mode	Notes	RP#	CE <sub>1</sub> #	CE <sub>0</sub> #	OE#	WE#	A <sub>1</sub>	DQ <sub>0-15</sub>	RY/BY#
Read	1,2,7	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	X	D <sub>OUT</sub>	X
Output Disable	1,6,7	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	X	High Z	X
Standby	1,6,7	V <sub>IH</sub>	V <sub>IL</sub> V <sub>IH</sub> V <sub>IH</sub>	V <sub>IL</sub> V <sub>IL</sub> V <sub>IH</sub>	X	X	X	High Z	X
Deep Power-Down	1,3	V <sub>IL</sub>	X	X	X	X	X	High Z	V <sub>OH</sub>
Manufacturer ID	4	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IL</sub>	0089H	V <sub>OH</sub>
Device ID	4	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	66A0H	V <sub>OH</sub>
Write	1,5,6	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IL</sub>	X	D <sub>IN</sub>	X

### 4.2 Bus Operations for Byte-Wide Mode (BYTE# = V<sub>IL</sub>)

Mode	Notes	RP#	CE <sub>1</sub> #	CE <sub>0</sub> #	OE#	WE#	A <sub>0</sub>	DQ <sub>0-7</sub>	RY/BY#
Read	1,2,7	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	X	D <sub>OUT</sub>	X
Output Disable	1,6,7	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	X	High Z	X
Standby	1,6,7	V <sub>IH</sub>	V <sub>IL</sub> V <sub>IH</sub> V <sub>IH</sub>	V <sub>IL</sub> V <sub>IL</sub> V <sub>IH</sub>	X	X	X	High Z	X
Deep Power-Down	1,3	V <sub>IL</sub>	X	X	X	X	X	High Z	V <sub>OH</sub>
Manufacturer ID	4	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IL</sub>	89H	V <sub>OH</sub>
Device ID	4	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	A0H	V <sub>OH</sub>
Write	1,5,6	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IL</sub>	X	D <sub>IN</sub>	X

#### NOTES:

1. X can be V<sub>IH</sub> or V<sub>IL</sub> for address or control pins except for RY/BY#, which is either V<sub>OL</sub> or V<sub>OH</sub>.
2. RY/BY# output is open drain. When the WSM is ready, Erase is suspended or the device is in deep power-down mode. RY/BY# will be at V<sub>OH</sub> if it is tied to V<sub>CC</sub> through a resistor. RY/BY# at V<sub>OH</sub> is independent of OE# while a WSM operation is in progress.
3. RP# at GND ± 0.2V ensures the lowest deep power-down current.
4. A<sub>0</sub> and A<sub>1</sub> at V<sub>IL</sub> provide device manufacturer codes in x8 and x16 modes respectively. A<sub>0</sub> and A<sub>1</sub> at V<sub>IH</sub> provide device ID codes in x8 and x16 modes respectively. All other addresses are set to zero.
5. Commands for Erase, Data Write, or Lock-Block operations can only be completed successfully when V<sub>pp</sub> = V<sub>ppH10r</sub> V<sub>pp</sub> = V<sub>ppH2</sub>.
6. While the WSM is running, RY/BY# in level-mode (default) stays at V<sub>OL</sub> until all operations are complete. RY/BY# goes to V<sub>OH</sub> when the WSM is not busy or in erase suspend mode.
7. RY/BY# may be at V<sub>OL</sub> while the WSM is busy performing various operations. For example, a Status Register read during a Write operation.

### 4.3 VE28F008 and M28F008 Compatible Mode Command Bus Definitions

Command	Notes	First Bus Cycle			Second Bus Cycle		
		Oper	Addr	Data	Oper	Addr	Data
Read Array		Write	X	FFH	Read	AA	AD
Intelligent Identifier	1	Write	X	90H	Read	IA	ID
Read Compatible Status Register	2	Write	X	70H	Read	X	CSRD
Clear Status Register	3	Write	X	50H			
Word/Byte Write		Write	X	40H	Write	WA	WD
Alternate Word/Byte Write		Write	X	10H	Write	WA	WD
Block Erase/Confirm		Write	X	20H	Write	BA	D0H
Erase Suspend/Resume		Write	X	B0H	Write	X	D0H

#### ADDRESS

AA = Array Address  
 BA = Block Address  
 IA = Identifier  
       Address  
 WA = Write Address  
 X = Don't Care

#### DATA

AD = Array Data  
 CSRD = CSR Data  
 ID = Identifier Data  
 WD = Write Data

#### NOTES:

1. Following the Intelligent Identifier command, two Read operations access the manufacturer and device signature codes.
2. The CSR is automatically available after device enters Data Write, Erase, or Suspend operations.
3. Clears CSR.3, CSR.4 and CSR.5. Also clears GSR.5 and all BSR.5 and BSR.2 bits. See Status Register definitions.

## 4.4 VS/MS28F016SV-Performance Enhancement Command Bus Definitions

Command	Mode	Notes	First Bus Cycle			Second Bus Cycle			Third Bus Cycle		
			Oper	Addr	Data	Oper	Addr	Data	Oper	Addr	Data
Read Extended Status Register		1	Write	X	71H	Read	RA	GSRD BSRD			
Page Buffer Swap		7	Write	X	72H						
Read Page Buffer			Write	X	75H	Read	PA	PD			
Single Load to Page Buffer			Write	X	74H	Write	PA	PD			
Sequential Load to Page Buffer	x8	4,6,10	Write	X	E0H	Write	X	BCL	Write	X	BCH
	x16	4,5,6,10	Write	X	E0H	Write	X	WCL	Write	X	WCH
Page Buffer Write to Flash	x8	3,4,9,10	Write	X	0CH	Write	A <sub>0</sub>	BC(L,H)	Write	WA	BC(H,L)
	x16	4,5,10	Write	X	0CH	Write	X	WCL	Write	WA	WCH
Two-Byte Write	x8	3	Write	X	FBH	Write	A <sub>0</sub>	WD(L,H)	Write	WA	WD(H,L)
Lock Block/Confirm			Write	X	77H	Write	BA	D0H			
Upload Status Bits/Confirm		2	Write	X	97H	Write	X	D0H			
Upload Device Information/Confirm			Write	X	99H	Write	X	D0H	Read	PA	PD
Erase All Unlocked Blocks/Confirm			Write	X	A7H	Write	X	D0H			
RY/BY# Enable to Level-Mode		8,11	Write	X	96H	Write	X	01H			
RY/BY# Pulse-On-Write		8,11	Write	X	96H	Write	X	02H			
RY/BY# Pulse-On-Erase		8,11	Write	X	96H	Write	X	03H			
RY/BY# Disable		8,11	Write	X	96H	Write	X	04H			
RY/BY# Pulse-On-Write/Erase		8, 11	Write	X	96H	Write	X	05H			
Sleep			Write	X	F0H						
Abort			Write	X	80H						

## ADDRESS

BA = Block Address

PA = Page Buffer Address

RA = Extended Register  
Address

WA = Write Address

X = Don't Care

AD = Array Data

PD = Page Buffer Data

BSRD = BSR Data

GSRD = GSR Data

## DATA

WC (L,H) = Word Count  
(Low, High)BC (L,H) = Byte Count  
(Low, High)WD (L,H) = Write Data  
(Low, High)

**NOTES:**

1. RA can be the GSR address or any BSR address. See Figures 4 and 5 for Extended Status Register memory maps.
2. Upon device power-up, all BSR lock-bits come up locked. The Upload Status Bits command must be written to reflect the actual lock-bit status.
3.  $A_0$  is automatically complemented to load second byte of data. BYTE# must be at  $V_{IL}$ .  $A_0$  value determines which WD/BC is supplied first:  $A_0 = 0$  looks at the WDL/BCL,  $A_0 = 1$  looks at the WDH/BCH.
4. BCH/WCH must be at 00H for this product because of the 256-byte (128-word) Page Buffer size, and to avoid writing the Page Buffer contents to more than one 256-byte segment within an array block. They are simply shown for future Page Buffer expandability.
5. In x16 mode, only the lower byte  $DQ_{0-7}$  is used for WCL and WCH. The upper byte  $DQ_{8-15}$  is a don't care.
6. PA and PD (whose count is given in cycles 2 and 3) are supplied starting in the fourth cycle, which is not shown.
7. This command allows the user to swap between available Page Buffers (0 or 1).
8. These commands reconfigure RY/BY# output to one of two pulse-modes or enable and disable the RY/BY# function.
9. Write address, WA, is the Destination address in the flash array which must match the Source address in the Page Buffer. Refer to the 28F016SA User's Manual.
10. BCL = 00H corresponds to a byte count of 1. Similarly, WCL = 00H corresponds to a word count of 1.
11. After writing the Upload Device Information command and the Confirm command, the following information is output at Page Buffer addresses specified below:

Device Information	
Address	Information
06H, 07H (Byte Mode)	Device Revision Number
03H (Word Mode)	Device Revision Number
1EH (Byte Mode)	Device Configuration Code
0FH ( $DQ_{0-7}$ ) (Word Mode)	Device Configuration Code
1FH (Byte Mode)	Device Proliferation Code (01H)
0FH ( $DQ_{8-15}$ ) (Word Mode)	Device Proliferation Code (01H)

The contents of all other Page Buffer locations, after the Upload Device Information command is written, are reserved for future implementation by Intel Corporation. See Section 4.8 for a description of the Device Configuration Code. This code also corresponds to data written to the VS/MS28F016SV after writing the RY/BY# Reconfiguration command.



#### 4.5 Compatible Status Register

WSMS	ESS	ES	DWS	VPPS	R	R	R
7	6	5	4	3	2	1	0

##### NOTES:

CSR.7 = WRITE STATE MACHINE STATUS

1 = Ready

0 = Busy

CSR.6 = ERASE-SUSPEND STATUS

1 = Erase Suspended

0 = Erase In Progress/Completed

CSR.5 = ERASE STATUS

1 = Error in Block Erasure

0 = Successful Block Erase

CSR.4 = DATA-WRITE STATUS

1 = Error in Data Write

0 = Data Write Successful

CSR.3 = Vpp STATUS

1 = Vpp Error Detect, Operation Abort

0 = Vpp OK

RY/BY# output or WSMS bit must be checked to determine completion of an operation (Erase, Erase Suspend, or Data Write) before the appropriate Status bit (ESS, ES or DWS) is checked for success.

If DWS and ES are set to "1" during an erase attempt, an improper command sequence was entered. Clear the CSR and attempt the operation again.

The VPPS bit, unlike an A/D converter, does not provide continuous indication of Vpp level. The WSM interrogates Vpp's level only after the Data-Write or Erase command sequences have been entered, and informs the system if Vpp has not been switched on. VPPS is not guaranteed to report accurate feedback between VppLK(max) and VppH1(min) and between VppH1(max) and VppH2(min).

CSR.2-0 = RESERVED FOR FUTURE ENHANCEMENTS

These bits are reserved for future use; mask them out when polling the CSR.

## 4.6 Global Status Register

WSMS	OSS	DOS	DSS	QS	PBAS	PBS	PBSS
7	6	5	4	3	2	1	0

### NOTES:

GSR.7 = WRITE STATE MACHINE STATUS

1 = Ready

0 = Busy

[1] RY/BY # output or WSMS bit must be checked to determine completion of an operation (Block Lock, Suspend, any RY/BY # reconfiguration, Upload Status Bits, Erase or Data Write) before the appropriate Status bit (OSS or DOS) is checked for success.

GSR.6 = OPERATION SUSPEND STATUS

1 = Operation Suspended

0 = Operation in Progress/Completed

GSR.5 = DEVICE OPERATION STATUS

1 = Operation Unsuccessful

0 = Operation Successful or Currently Running

GSR.4 = DEVICE SLEEP STATUS

1 = Device in Sleep

0 = Device Not in Sleep

MATRIX 5/4

00 = Operation Successful or Currently Running

If operation currently running, then GSR.7 = 0.

01 = Device in Sleep mode or Pending Sleep

If device pending sleep, then GSR.7 = 0.

10 = Operation Unsuccessful

11 = Operation Unsuccessful or Aborted

Operation aborted: Unsuccessful due to Abort command.

GSR.3 = QUEUE STATUS

1 = Queue Full

0 = Queue Available

GSR.2 = PAGE BUFFER AVAILABLE STATUS

1 = One or Two Page Buffers Available

The device contains two Page Buffers.

0 = No Page Buffer Available

GSR.1 = PAGE BUFFER STATUS

1 = Selected Page Buffer Ready

0 = Selected Page Buffer Busy

Selected Page Buffer is currently busy with WSM operation

GSR.0 = PAGE BUFFER SELECT STATUS

1 = Page Buffer 1 Selected

0 = Page Buffer 0 Selected

### NOTE:

1. When multiple operations are queued, checking BSR.7 only provides indication of completion for that particular block. GSR.7 provides indication when all queued operations are completed.

## 4.7 Block Status Register

BS	BLS	BOS	BOAS	QS	VPPS	VPPL	R
7	6	5	4	3	2	1	0

**NOTES:**

BSR.7 = BLOCK STATUS

1 = Ready

0 = Busy

BSR.6 = BLOCK LOCK STATUS

1 = Block Unlocked for Write/Erase

0 = Block Locked for Write/Erase

BSR.5 = BLOCK OPERATION STATUS

1 = Operation Unsuccessful

0 = Operation Successful or

Currently Running

BSR.4 = BLOCK OPERATION ABORT STATUS

1 = Operation Aborted

0 = Operation Not Aborted

MATRIX 5/4

00 = Operation Successful or

Currently Running

01 = Not a Valid Combination

10 = Operation Unsuccessful

11 = Operation Aborted

BSR.3 = QUEUE STATUS

1 = Queue Full

0 = Queue Available

BSR.2 = V<sub>PP</sub> STATUS1 = V<sub>PP</sub> Error Detect, Operation Abort0 = V<sub>PP</sub> OKBSR.1 = V<sub>PP</sub> LEVEL1 = V<sub>PP</sub> Detected at 5.0V ± 10%0 = V<sub>PP</sub> Detected at 12.0V ± 5%

[1] RY/BY# output or BS bit must be checked to determine completion of an operation (Block Lock, Suspend, Erase or Data Write) before the appropriate Status bits (BOS, BLS) is checked for success.

The BOAS bit will not be set until BSR.7 = 1.

Operation halted via Abort command.

BSR.1 is not guaranteed to report accurate feedback between the V<sub>PPH1</sub> and V<sub>PPH2</sub> voltage ranges. Writes and erases with V<sub>PP</sub> between V<sub>PLLK</sub>(max) and V<sub>PPH1</sub>(min), between V<sub>PPH1</sub>(max) and V<sub>PPH2</sub>(min), and above V<sub>PPH2</sub>(max) produce spurious results and should not be attempted. BSR.1 was a RESERVED bit on the 28F016SA.

BSR.0 = RESERVED FOR FUTURE ENHANCEMENTS

These bits are reserved for future use; mask them out when polling the BSRs.

**NOTE:**

1. When multiple operations are queued, checking BSR.7 only provides indication of completion or that particular block. GSR.7 provides indication when all queued operations are completed.

**4.8 Device Configuration Code**

R	R	R	R	R	RB2	RB1	RB0
7	6	5	4	3	2	1	0

**NOTES:**

DCC.2-DCC.0 = RY/BY# CONFIGURATION (RB2-RB0)

001 = Level Mode (Default)

010 = Pulse-On-Write

011 = Pulse-On-Erase

100 = RY/BY# Disabled

101 = Pulse-On-Write/Erase

Undocumented combinations of RB2-RB0 are reserved by Intel Corporation for future implementations and should not be used.

DCC.7-DCC.3 = RESERVED FOR FUTURE ENHANCEMENTS

These bits are reserved for future use; mask them out when reading the Device Configuration Code.

Set these bits to "0" when writing the desired RY/BY# configuration to the device.

## 5.0 ELECTRICAL SPECIFICATIONS

### 5.1 Absolute Maximum Ratings

Temperature Under Bias

- SE1 ..... –55°C to +125°C
- SE2 ..... –40°C to +125°C

Storage Temperature ..... –65° to +125°C

NOTICE: This data sheet contains information on products in the sampling and initial production phases of development. The specifications are subject to change without notice. Verify with your local Intel Sales office that you have the latest data sheet before finalizing a design.

*\*WARNING: Stressing the device beyond the "Absolute Maximum Ratings" may cause permanent damage. These are stress ratings only. Operation beyond the "Operating Conditions" is not recommended and extended exposure beyond the "Operating Conditions" may affect device reliability.*

**V<sub>CC</sub> = 3.3V ± 0.3V Systems(4)**

Sym	Parameter	Notes	Min	Max	Units	Test Conditions
T <sub>ASE2</sub>	Operating Temperature, SE2		–40	+125	°C	
T <sub>ASE1</sub>	Operating Temperature, SE1		–55	+125	°C	
V <sub>CC</sub>	V <sub>CC</sub> with Respect to GND	1	–0.2	7.0	V	
V <sub>PP</sub>	V <sub>PP</sub> Supply Voltage with Respect to GND	1,2	–0.2	14.0	V	
V	Voltage on any Pin (except V <sub>CC</sub> , V <sub>PP</sub> ) with Respect to GND	1	–0.5	V <sub>CC</sub> + 0.5	V	
I	Current into any Non-Supply Pin			±30	mA	
I <sub>OUT</sub>	Output Short Circuit Current	3		100	mA	

**V<sub>CC</sub> = 5.0V ± 0.5V, V<sub>CC</sub> = 5.0V ± 0.25V Systems(4, 5)**

Sym	Parameter	Notes	Min	Max	Units	Test Conditions
T <sub>ASE2</sub>	Operating Temperature, SE2		–40	+125	°C	
T <sub>ASE1</sub>	Operating Temperature, SE1		–55	+125	°C	
V <sub>CC</sub>	V <sub>CC</sub> with Respect to GND	1	–0.2	7.0	V	
V <sub>PP</sub>	V <sub>PP</sub> Supply Voltage with Respect to GND	1,2	–0.2	14.0	V	
V	Voltage on any Pin (except V <sub>CC</sub> , V <sub>PP</sub> ) with Respect to GND	1	–2.0	7.0	V	
I	Current into any Non-Supply Pin			±30	mA	
I <sub>OUT</sub>	Output Short Circuit Current	3		100	mA	

**NOTES:**

1. Minimum DC voltage is –0.5V on input/output pins. During transitions, this level may undershoot to –2.0V for periods <20 ns. Maximum DC voltage on input/output pins is V<sub>CC</sub> + 0.5V which, during transitions, may overshoot to V<sub>CC</sub> + 2.0V for periods <20 ns.
2. Maximum DC voltage on V<sub>PP</sub> may overshoot to +14.0V for periods <20 ns.
3. Output shorted for no more than one second. No more than one output shorted at a time.
4. AC specifications are valid at both voltage ranges. See DC Characteristics tables for voltage range-specific specifications.
5. 5% V<sub>CC</sub> specifications refer to the VS/MS28F016SV-80 in its high speed test configuration.

## 5.2 Capacitance

**For a 3.3V System:**

Sym	Parameter	Notes	Typ	Max	Units	Test Conditions
C <sub>IN</sub>	Capacitance Looking into an Address/Control Pin	1	6	8	pF	T <sub>A</sub> = 25°C, f = 1.0 MHz
C <sub>OUT</sub>	Capacitance Looking into an Output Pin	1	8	12	pF	T <sub>A</sub> = 25°C, f = 1.0 MHz
C <sub>LOAD</sub>	Load Capacitance Driven by Outputs for Timing Specifications	1		50	pF	For V <sub>CC</sub> = 3.3V ± 0.3V
	Equivalent Load Timing Circuit			2.5	ns	50Ω transmission line delay

**For a 5.0V System:**

Sym	Parameter	Notes	Typ	Max	Units	Test Conditions
C <sub>IN</sub>	Capacitance Looking into an Address/Control Pin	1	6	8	pF	T <sub>A</sub> = 25°C, f = 1.0 MHz
C <sub>OUT</sub>	Capacitance Looking into an Output Pin	1	8	12	pF	T <sub>A</sub> = 25°C, f = 1.0 MHz
C <sub>LOAD</sub>	Load Capacitance Driven by Outputs for Timing Specifications	1		100	pF	For V <sub>CC</sub> = 5.0V ± 0.5V
				30	pF	For V <sub>CC</sub> = 5.0V ± 0.25V
	Equivalent Testing Load Circuit for V <sub>CC</sub> ± 10%			2.5	ns	25Ω transmission line delay
	Equivalent Testing Load Circuit for V <sub>CC</sub> ± 5%			2.5	ns	85Ω transmission line delay

**NOTE:**

1. Sampled, not 100% tested.

### 5.3 Timing Nomenclature

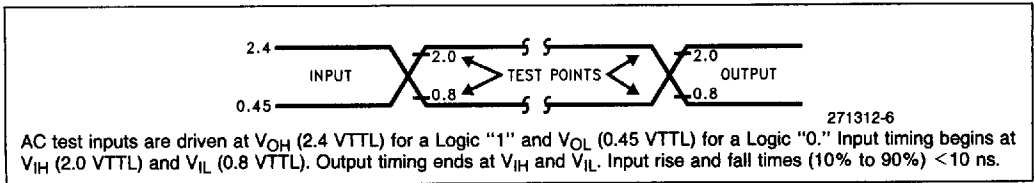
All 3.3V system timings are measured from where signals cross 1.5V.

For 5.0V systems use the standard JEDEC cross point definitions.

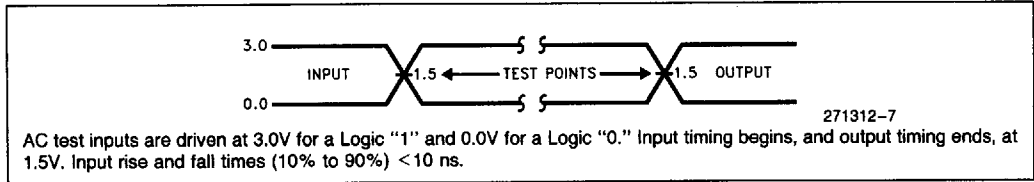
Each timing parameter consists of 5 characters. Some common examples are defined as follows:

$t_{CE}$	$t_{ELQV}$ time(t) from CE # (E) going low (L) to the outputs (Q) becoming valid (V)
$t_{OE}$	$t_{GLQV}$ time(t) from OE # (G) going low (L) to the outputs (Q) becoming valid (V)
$t_{ACC}$	$t_{AVQV}$ time(t) from address (A) valid (V) to the outputs (Q) becoming valid (V)
$t_{AS}$	$t_{AVWH}$ time(t) from address (A) valid (V) to WE # (W) going high (H)
$t_{DH}$	$t_{WHDH}$ time(t) from WE # (W) going high (H) to when the data (D) can become undefined (X)

	Pin Characters		Pin States
A	Address Inputs	H	High
D	Data Inputs	$\bar{L}$	Low
Q	Data Outputs	V	Valid
E	CE # (Chip Enable)	X	Driven, but not necessarily valid
F	BYTE # (Byte Enable)	Z	High Impedance
G	OE # (Output Enable)		
W	WE # (Write Enable)		
P	RP # (Deep Power-Down Pin)		
R	RY/BY # (Ready Busy)		
V	Any Voltage Level		
5V	V <sub>CC</sub> at 4.5V Minimum		
3V	V <sub>CC</sub> at 3.0V Minimum		

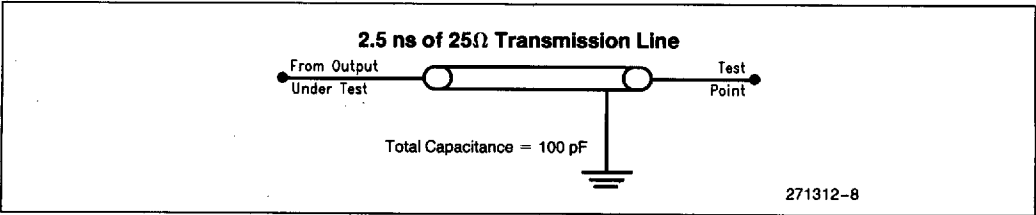


**Figure 6. Transient Input/Output Reference Waveform ( $V_{CC} = 5.0V \pm 10\%$ )**

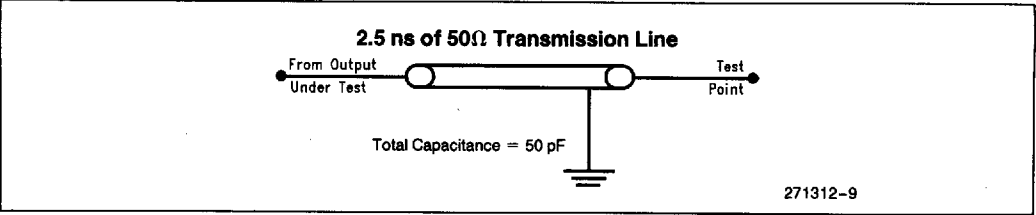


**Figure 7. Transient Input/Output Reference Waveform ( $V_{CC} = 3.3V \pm 10\%$ )**  
**High Speed Reference Waveform ( $V_{CC} = 5.0V \pm 5\%$ )**

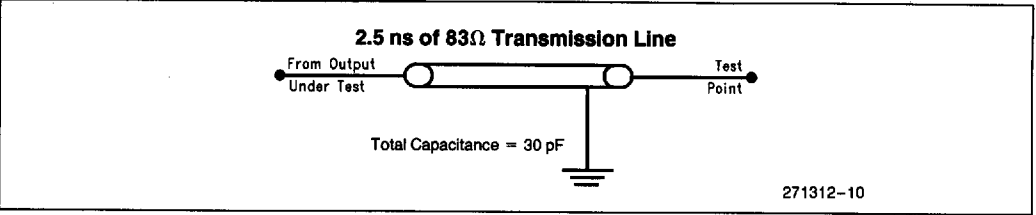




**Figure 8. Transient Equivalent Testing Load Circuit ( $V_{CC} = 5.0V \pm 10\%$ )**



**Figure 9. Transient Equivalent Testing Load Circuit ( $V_{CC} = 3.3V \pm 10\%$ )**



**Figure 10. High Speed Transient Equivalent Testing Load Circuit ( $V_{CC} = 5.0V \pm 5\%$ )**

**5.4 DC Characteristics**
 $V_{CC} = 3.3V \pm 0.3V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ 

Sym	Parameter	Notes	Min	Max	Units	Test Conditions
$I_{LI}$	Input Load Current	1		$\pm 1$	$\mu A$	$V_{CC} = V_{CC} \text{ Max}$ , $V_{IN} = V_{CC} \text{ or GND}$
$I_{LO}$	Output Leakage Current	1		$\pm 10$	$\mu A$	$V_{CC} = V_{CC} \text{ Max}$ , $V_{IN} = V_{CC} \text{ or GND}$
$I_{CCS}$	$V_{CC}$ Standby Current	1,5		130	$\mu A$	$V_{CC} = V_{CC} \text{ Max}$ , $CE_0\#, CE_1\#, RP\# = V_{CC} \pm 0.2V$ $BYTE\#, WP\# = V_{CC} \pm 0.2V$ or $GND \pm 0.2V$
				4	mA	$V_{CC} = V_{CC} \text{ Max}$ , $CE_0\#, CE_1\#, RP\# = V_{IH}$ $BYTE\#, WP\# = V_{IH} \text{ or } V_{IL}$
$I_{CCD}$	$V_{CC}$ Deep Power-Down Current	1		50	$\mu A$	$RP\# = GND \pm 0.2V$ $BYTE\# = V_{CC} \pm 0.2V$ or $GND \pm 0.2V$
$I_{CCR1}$	$V_{CC}$ Read Current	1,4,5		60	mA	$V_{CC} = V_{CC} \text{ Max}$ CMOS: $CE_0\#, CE_1\# = GND \pm 0.2V$ $BYTE\# = GND \pm 0.2V$ or $V_{CC} \pm 0.2V$ Inputs = $GND \pm 0.2V$ or $V_{CC} \pm 0.2V$ TTL: $CE_0\#, CE_1\# = V_{IL}$ , $BYTE\# = V_{IL} \text{ or } V_{IH}$ INPUTS = $V_{IL} \text{ or } V_{IH}$ , $f = 8 \text{ MHz}$ , $I_{OUT} = 0 \text{ mA}$
$I_{CCR2}$	$V_{CC}$ Read Current	1,4,5		40	mA	$V_{CC} = V_{CC} \text{ Max}$ CMOS: $CE_0\#, CE_1\# = GND \pm 0.2V$ $BYTE\# = GND \pm 0.2V$ or $V_{CC} \pm 0.2V$ Inputs = $GND \pm 0.2V$ or $V_{CC} \pm 0.2V$ TTL: $CE_0\#, CE_1\# = V_{IL}$ , $BYTE\# = V_{IL} \text{ or } V_{IH}$ INPUTS = $V_{IL} \text{ or } V_{IH}$ , $f = 4 \text{ MHz}$ , $I_{OUT} = 0 \text{ mA}$

**5.4 DC Characteristics** (Continued)
 $V_{CC} = 3.3V \pm 0.3V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ 

Sym	Parameter	Notes	Min	Max	Units	Test Conditions
I <sub>CCW</sub>	V <sub>CC</sub> Write Current	1		12	mA	Word/Byte Write in Progress V <sub>pp</sub> = 12.0V ± 5%
				17	mA	Word/Byte Write in Progress V <sub>pp</sub> = 5.0V ± 10%
I <sub>OCE</sub>	V <sub>CC</sub> Block Erase Current	1		12	mA	Block Erase in Progress V <sub>pp</sub> = 12.0V ± 5%
				17	mA	Block Erase in Progress V <sub>pp</sub> = 5.0V ± 10%
I <sub>CCES</sub>	V <sub>CC</sub> Erase Suspend Current	1,2		6	mA	CE <sub>0</sub> #, CE <sub>1</sub> # = V <sub>IH</sub> Block Erase Suspended
I <sub>PPS</sub> I <sub>PPR</sub>	V <sub>pp</sub> Standby/Read Current	1		±15	μA	V <sub>pp</sub> ≤ V <sub>CC</sub>
				200	μA	V <sub>pp</sub> > V <sub>CC</sub>
I <sub>PPD</sub>	V <sub>pp</sub> Deep Power-Down Current	1		50	μA	RP# = GND ± 0.2V
I <sub>PPW</sub>	V <sub>pp</sub> Write Current	1		15	mA	V <sub>pp</sub> = 12.0V ± 5% Word/Byte Write in Progress
				25	mA	V <sub>pp</sub> = 5.0V ± 10% Word/Byte Write in Progress
I <sub>PPE</sub>	V <sub>pp</sub> Erase Current	1		10	mA	V <sub>pp</sub> = 12.0V ± 5% Block Erase in Progress
				20	mA	V <sub>pp</sub> = 5.0V ± 10% Block Erase in Progress
I <sub>PPES</sub>	V <sub>pp</sub> Erase Suspend Current	1		200	μA	V <sub>pp</sub> = V <sub>ppH1</sub> or V <sub>ppH2</sub> Block Erase Suspended
V <sub>IL</sub>	Input Low Voltage		-0.3	0.8	V	
V <sub>IH</sub>	Input High Voltage		2.0	V <sub>CC</sub> + 0.3	V	
V <sub>OL</sub>	Output Low Voltage			0.4	V	V <sub>CC</sub> = V <sub>CC</sub> Min and I <sub>OL</sub> = 4 mA

**5.4 DC Characteristics (Continued)**
 $V_{CC} = 3.3V \pm 0.3V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ 

Sym	Parameter	Notes	Min	Max	Units	Test Conditions
$V_{OH1}$	Output High Voltage		2.4		V	$I_{OH} = -2.0\text{ mA}$ $V_{CC} = V_{CC}\text{ Min}$
$V_{OH2}$			$V_{CC} - 0.2$		V	$I_{OH} = -100\text{ }\mu A$ $V_{CC} = V_{CC}\text{ Min}$
$V_{PPLK}$	$V_{pp}$ Erase/Write Lock Voltage	3	0.0	1.8	V	
$V_{PPH1}$	$V_{pp}$ during Write/Erase Operations	3	4.5	5.5	V	
$V_{PPH2}$	$V_{pp}$ during Write/Erase Operations	3	11.4	12.6	V	
$V_{LKO}$	$V_{CC}$ Erase/Write Lock Voltage		1.8		V	

**NOTES:**

1. All currents are in RMS unless otherwise noted. These currents are valid for all product versions (package and speeds).
2.  $I_{CCES}$  is specified with the device de-selected. If the device is read while in erase suspend mode, current draw is the sum of  $I_{CCES}$  and  $I_{CCR}$ .
3. Block Erases, Word/Byte Writes and Lock Block operations are inhibited when  $V_{pp} \leq V_{PPLK}$  and not guaranteed in the ranges between  $V_{PPLK}(\text{max})$  and  $V_{PPH1}(\text{min})$ , between  $V_{PPH1}(\text{max})$  and  $V_{PPH2}(\text{min})$  and above  $V_{PPH2}(\text{max})$ .
4. Automatic Power Savings (APS) reduces  $I_{CCR}$  to less than 3 mA in static operation.
5. CMOS Inputs are either  $V_{CC} \pm 0.2V$  or  $GND \pm 0.2V$ . TTL Inputs are either  $V_{IL}$  or  $V_{IH}$ .

## 5.5 DC Characteristics

 $V_{CC} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ 

Sym	Parameter	Notes	Min	Max	Units	Test Conditions
$I_{IL}$	Input Load Current	1		$\pm 1$	$\mu A$	$V_{CC} = V_{CC} \text{ Max}$ $V_{IN} = V_{CC} \text{ or GND}$
$I_{LO}$	Output Leakage Current	1		$\pm 10$	$\mu A$	$V_{CC} = V_{CC} \text{ Max}$ $V_{IN} = V_{CC} \text{ or GND}$
$I_{CCS}$	$V_{CC}$ Standby Current	1,5		130	$\mu A$	$V_{CC} = V_{CC} \text{ Max}$ $CE_0\#, CE_1\#, RP\# = V_{CC} \pm 0.2V$ $BYTE\#, WP\# = V_{CC} \pm 0.2V \text{ or GND} \pm 0.2V$
				4	mA	$V_{CC} = V_{CC} \text{ Max}$ $CE_0\#, CE_1\#, RP\# = V_{IH}$ $BYTE\#, WP\# = V_{IH} \text{ or } V_{IL}$
$I_{CCD}$	$V_{CC}$ Deep Power-Down Current	1		50	$\mu A$	$RP\# = GND \pm 0.2V$ $BYTE\# = V_{CC} \pm 0.2V \text{ or GND} \pm 0.2V$
$I_{CCR1}$	$V_{CC}$ Read Current	1,4,5		135	mA	$V_{CC} = V_{CC} \text{ Max}$ , CMOS: $CE_0\#, CE_1\# = GND \pm 0.2V$ $BYTE\# = GND \pm 0.2V \text{ or } V_{CC} \pm 0.2V$ Inputs = $GND \pm 0.2V \text{ or } V_{CC} \pm 0.2V$ TTL: $CE_0\#, CE_1\# = V_{IL}$ , $BYTE\# = V_{IL} \text{ or } V_{IH}$ Inputs = $V_{IL} \text{ or } V_{IH}$ , $f = 10 \text{ MHz}$ , $I_{OUT} = 0 \text{ mA}$
$I_{CCR2}$	$V_{CC}$ Read Current	1,4,5		90	mA	$V_{CC} = V_{CC} \text{ Max}$ , CMOS: $CE_0\#, CE_1\# = GND \pm 0.2V$ $BYTE\# = GND \pm 0.2V \text{ or } V_{CC} \pm 0.2V$ Inputs = $GND \pm 0.2V \text{ or } V_{CC} \pm 0.2V$ TTL: $CE_0\#, CE_1\# = V_{IL}$ , $BYTE\# = V_{IL} \text{ or } V_{IH}$ Inputs = $V_{IL} \text{ or } V_{IH}$ , $f = 5 \text{ MHz}$ , $I_{OUT} = 0 \text{ mA}$

**5.5 DC Characteristics** (Continued)

 $V_{CC} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ 

Sym	Parameter	Notes	Min	Max	Units	Test Conditions
I <sub>CCW</sub>	V <sub>CC</sub> Write Current	1		35	mA	Word/Byte in Progress V <sub>pp</sub> = 12.0V $\pm$ 5%
				40	mA	Word/Byte in Progress V <sub>pp</sub> = 5.0V $\pm$ 10%
I <sub>CCE</sub>	V <sub>CC</sub> Block Erase Current	1		25	mA	Block Erase in Progress V <sub>pp</sub> = 12.0V $\pm$ 5%
				30	mA	Block Erase in Progress V <sub>pp</sub> = 5.0V $\pm$ 10%
I <sub>CCES</sub>	V <sub>CC</sub> Erase Suspend Current	1, 2		10	mA	CE <sub>0</sub> #, CE <sub>1</sub> # = V <sub>IH</sub> Block Erase Suspended
I <sub>PPS</sub> I <sub>PPR</sub>	V <sub>pp</sub> Standby/Read Current	1		$\pm$ 15	$\mu$ A	V <sub>pp</sub> $\leq$ V <sub>CC</sub>
				200	$\mu$ A	V <sub>pp</sub> > V <sub>CC</sub>
I <sub>PPD</sub>	V <sub>pp</sub> Deep Power-Down Current	1		30	$\mu$ A	RP# = GND $\pm$ 0.2V
I <sub>PPW</sub>	V <sub>pp</sub> Write Current	1		12	mA	V <sub>pp</sub> = 12.0V $\pm$ 5% Word/Byte Write in Progress
				22	mA	V <sub>pp</sub> = 5.0V $\pm$ 10% Word/Byte Write in Progress
I <sub>PPE</sub>	V <sub>pp</sub> Block Erase Current	1		10	mA	V <sub>pp</sub> = 12.0V $\pm$ 5% Block Erase in Progress
				20	mA	V <sub>pp</sub> = 5.0V $\pm$ 10% Block Erase in Progress
I <sub>PPES</sub>	V <sub>pp</sub> Erase Suspend Current	1		200	$\mu$ A	V <sub>pp</sub> = V <sub>ppH1</sub> or V <sub>ppH2</sub> , Block Erase Suspended
V <sub>IL</sub>	Input Low Voltage		-0.5	0.8	V	
V <sub>IH</sub>	Input High Voltage		2.0	V <sub>CC</sub> + 0.5	V	

**5.5 DC Characteristics** (Continued) $V_{CC} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ 

Sym	Parameter	Notes	Min	Max	Units	Test Conditions
$V_{OL}$	Output Low Voltage			0.45	V	$V_{CC} = V_{CC} \text{ Min}$ $I_{OL} = 5.8 \text{ mA}$
$V_{OH1}$	Output High Voltage		0.85 $V_{CC}$		V	$I_{OH} = -2.5 \text{ mA}$ $V_{CC} = V_{CC} \text{ Min}$
$V_{OH2}$			$V_{CC}$ -0.4			$I_{OH} = -100 \mu A$ $V_{CC} = V_{CC} \text{ Min}$
$V_{PPLK}$	$V_{PP}$ Write/Erase Lock Voltage	3	0.0	1.8	V	
$V_{PPH1}$	$V_{PP}$ during Write/Erase Operations		4.5	5.5	V	
$V_{PPH2}$	$V_{PP}$ during Write/Erase Operations		11.4	12.6	V	
$V_{LKO}$	$V_{CC}$ Write/Erase Lock Voltage		1.8		V	

**NOTES:**

1. All currents are in RMS unless otherwise noted. These currents are valid for all product versions (package and speeds).
2.  $I_{CCES}$  is specified with the device de-selected. If the device is read while in erase suspend mode, current draw is the sum of  $I_{CCES}$  and  $I_{CCR}$ .
3. Block Erases, Word/Byte Writes and Lock Block operations are inhibited when  $V_{PP} \leq V_{PPLK}$  and not guaranteed in the ranges between  $V_{PPLK}(\text{max})$  and  $V_{PPH1}(\text{min})$ , between  $V_{PPH1}(\text{max})$  and  $V_{PPH2}(\text{min})$  and above  $V_{PPH2}(\text{max})$ .
4. Automatic Power Saving (APS) reduces  $I_{CCR}$  to less than 1 mA in Static operation.
5. CMOS Inputs are either  $V_{CC} \pm 0.2V$  or  $GND \pm 0.2V$ . TTL Inputs are either  $V_{IL}$  or  $V_{IH}$ .

**5.6 AC Characteristics—Read Only Operations<sup>(1)</sup>**
 $V_{CC} = 3.3V \pm 0.3V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 50 pF

Versions					Units
Sym	Parameter	Notes	Min	Max	
$t_{AVAV}$	Read Cycle Time		120		ns
$t_{AVEL}$	Address Setup to CE # Going Low	3	0		
$t_{AVGL}$	Address Setup to OE # Going Low	3	0		
$t_{AVQV}$	Address to Output Delay ( $T_{ACC}$ )			120	ns
$t_{ELQV}$	CE # to Output Delay ( $T_{CE}$ )	2		120	ns
$t_{PHQV}$	RP # High to Output Delay			620	ns
$t_{GLQV}$	OE # to Output Delay ( $T_{OE}$ )	2		45	ns
$t_{ELQX}$	CE # to Output in Low Z	3	0		ns
$t_{EHQZ}$	CE # to Output in High Z	3		50	ns
$t_{GLQX}$	OE # to Output in Low Z	3	0		ns
$t_{GHQZ}$	OE # to Output in High Z	3		30	ns
$t_{OH}$	Output Hold from Address, CE # or OE # Change, Whichever Occurs First	3	0		ns
$t_{FLQV}$ $t_{FHQV}$	BYTE # to Output Delay	3		120	ns
$t_{FLQZ}$	BYTE # Low to Output in High Z	3		30	ns
$t_{ELFL}$ $t_{ELFH}$	CE # Low to BYTE # High or Low	3		5	ns



**5.6 AC Characteristics—Read Only Operations<sup>(1)</sup>** (Continued)

$V_{CC} = 5.0V \pm 0.25V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 30 pF  
 $V_{CC} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 100 pF

Versions <sup>(4)</sup>			$V_{CC} \pm 5\%$ <sup>(5)</sup>		$V_{CC} \pm 10\%$ <sup>(6)</sup>		Unit
Sym	Parameter	Notes	Min	Max	Min	Max	
$t_{AVAV}$	Read Cycle Time		80		85		ns
$t_{AVEL}$	Address Setup to CE# Going Low	3	0		0		ns
$t_{AVGL}$	Address Setup to OE# Going Low	3	0		0		ns
$t_{AVQV}$	Address to Output Delay ( $T_{ACC}$ )			80		85	ns
$t_{ELQV}$	CE# to Output Delay ( $T_{CE}$ )	2		80		85	ns
$t_{PHQV}$	RP# to Output Delay			400		480	ns
$t_{GLQV}$	OE# to Output Delay ( $T_{OE}$ )	2		30		35	ns
$t_{ELQX}$	CE# to Output in Low Z	3	0		0		ns
$t_{EHQZ}$	CE# to Output in High Z	3		25		30	ns
$t_{GLQX}$	OE# to Output in Low Z	3	0		0		ns
$t_{GHQZ}$	OE# to Output in High Z	3		25		30	ns
$t_{OH}$	Output Hold from Address, CE# or OE# Change, Whichever Occurs First	3	0		0		ns
$t_{FLQV}$ $t_{FHQV}$	BYTE# to Output Delay	3		80		85	ns
$t_{FLQZ}$	BYTE# Low to Output in High Z	3		25		30	ns
$t_{ELFL}$ $t_{ELFH}$	CE# Low to BYTE# High or Low	3		5		5	ns

**NOTES:**

CE<sub>x</sub># is defined as the latter of CE<sub>0</sub># or CE<sub>1</sub># going low, or the first of CE<sub>0</sub># or CE<sub>1</sub># going high.

1. See AC Input/Output Reference Waveforms for timing measurements, Figures 6 and 7.

2. OE# may be delayed up to  $t_{ELQV}$ - $t_{GLQV}$  after the falling edge of CE#, without impacting  $t_{ELQV}$ .

3. Sampled, not 100% tested.

4. Device speeds are defined as:

80/85 ns at  $V_{CC} = 5.0V$  equivalent to

120 ns at  $V_{CC} = 3.3V$

5. See the high speed AC Input/Output Reference Waveforms and AC Testing Load Circuit.

6. See the standard AC Input/Output Reference Waveforms and AC Testing Load Circuit.

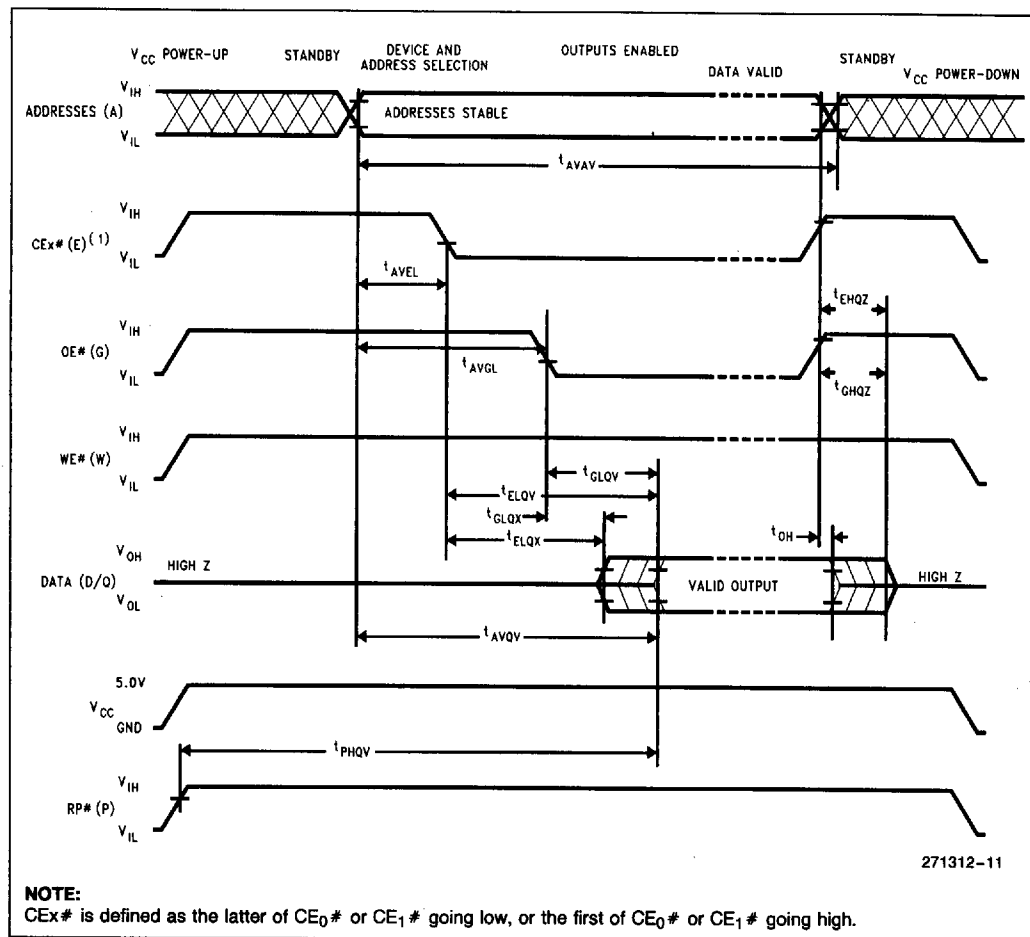


Figure 11. Read Timing Waveforms

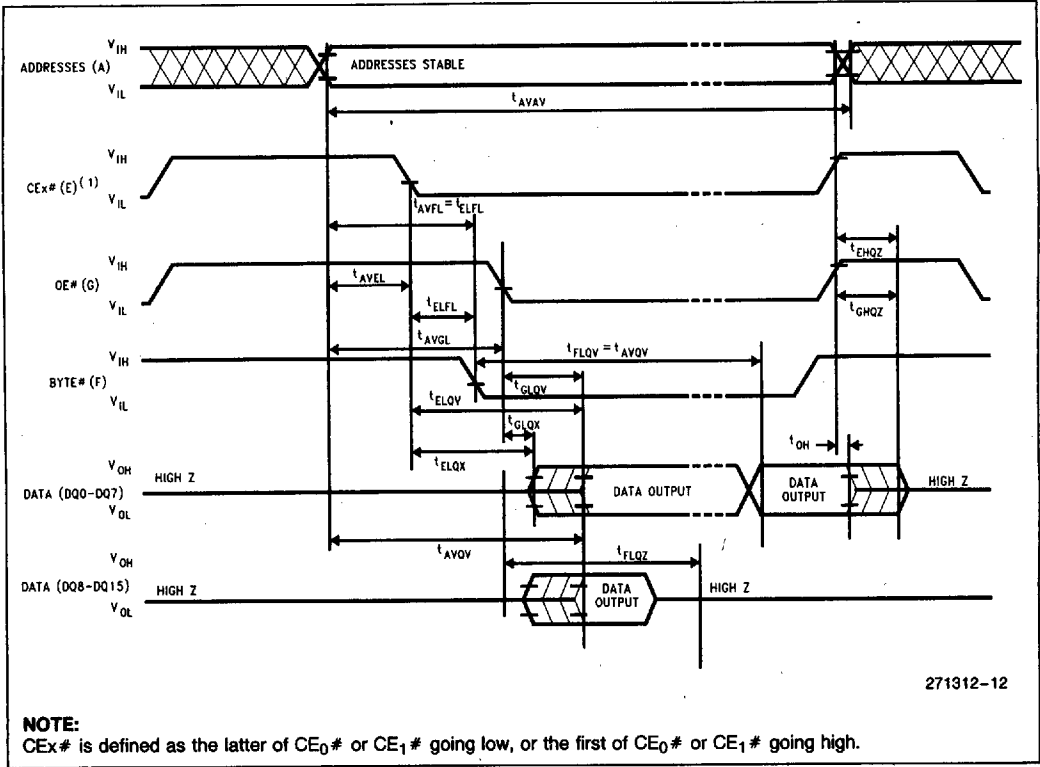


Figure 12. BYTE # Timing Waveforms

## 5.7 Power-Up and Reset Timings

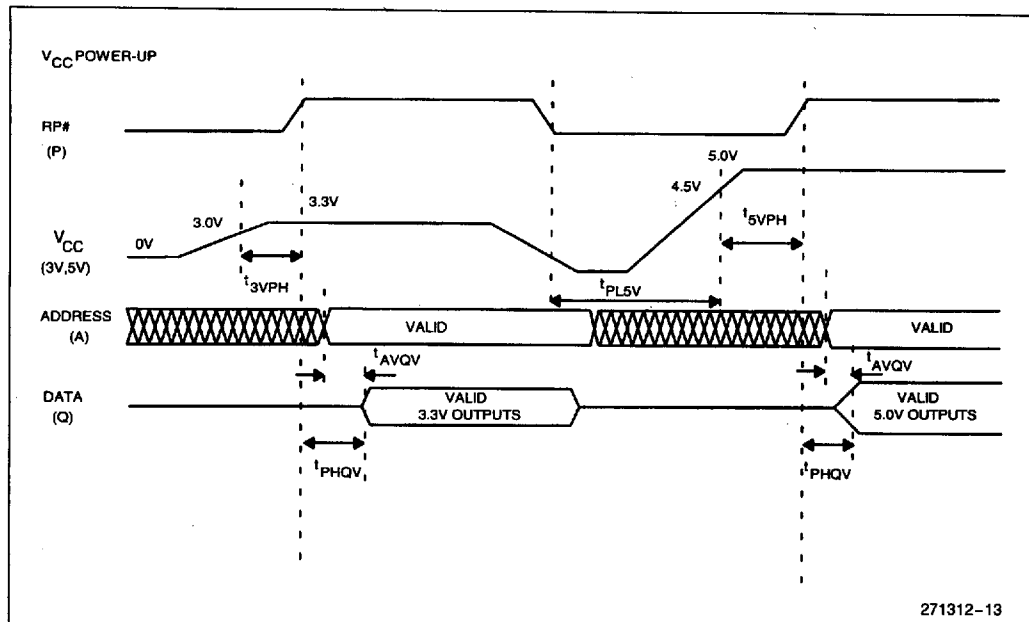


Figure 13. V<sub>CC</sub> Power-Up and RP# Reset Waveforms

4

Sym	Parameter	Notes	Min	Max	Unit	Test Conditions
t <sub>PL5V</sub> t <sub>PL3V</sub>	RP# Low to V <sub>CC</sub> at 4.5V minimum (to V <sub>CC</sub> at 3.0V min or 3.6V max)	2	0		μs	
t <sub>AVQV</sub>	Address Valid to Data Valid for V <sub>CC</sub> = 5.0V ± 10%	3		80	ns	
t <sub>PHQV</sub>	RP# High to Data Valid for V <sub>CC</sub> = 5.0V ± 10%	3		480	ns	
t <sub>5VPH</sub>	V <sub>CC</sub> at 4.5V (minimum) to RP# High	1	2	2	μs	CMOS (V <sub>CC</sub> ± 0.2V)
			0.002	1.5	ms	TTL (V <sub>IH</sub> (MIN) = 2.0V)
t <sub>3VPH</sub>	V <sub>CC</sub> at 4.5V (minimum) to RP# High	1	2		μs	

### NOTES:

CE<sub>0</sub>#, CE<sub>1</sub># and OE# are switched low after Power-Up.

1. The t<sub>5VPH</sub> and/or t<sub>3VPH</sub> times must be strictly followed to guarantee all other read and write specifications for the VS/MS28F016SV.

2. The power supply may start to switch concurrently with RP# going low.

3. The address access time and RP# high to data valid time are shown for 5.0V V<sub>CC</sub> operation. Refer to the AC Characteristics-Read Only Operations, 3.3V V<sub>CC</sub>.

**5.8 AC Characteristics for WE #—Controlled Command Write Operations<sup>(1)</sup>**V<sub>CC</sub> = 3.3V ± 0.3V, T<sub>ASE2</sub> = -40°C to +125°C, T<sub>ASE1</sub> = -55°C to +125°C, Load = 50 pF

Versions					Unit
Sym	Parameter	Notes	Min	Max	
t <sub>AVAV</sub>	Write Cycle Time		120		ns
t <sub>VPWH</sub>	V <sub>PP</sub> Setup to WE # Going High	3	100		ns
t <sub>PHEL</sub>	RP # Setup to CE # Going Low		480		ns
t <sub>ELWL</sub>	CE # Setup to WE # Going Low		10		ns
t <sub>AVWH</sub>	Address Setup to WE # Going High	2,6	75		ns
t <sub>DVWH</sub>	Data Setup to WE # Going High	2,6	75		ns
t <sub>WLWH</sub>	WE # Pulse Width		75		ns
t <sub>WHDX</sub>	Data Hold from WE # High	2	10		ns
t <sub>WHAX</sub>	Address Hold from WE # High	2	10		ns
t <sub>WHEH</sub>	CE # Hold from WE # High		10		ns
t <sub>WHWL</sub>	WE # Pulse Width High		45		ns
t <sub>GHWL</sub>	Read Recovery before Write		0		ns
t <sub>WHRL</sub>	WE # High to RY/BY # Going Low			100	ns
t <sub>RHPL</sub>	RP # Hold from Valid Status Register (CSR, GSR, BSR) Data and RY/BY # High	3	0		ns
t <sub>PHWL</sub>	RP # High Recovery to WE # Going Low		480		ns
t <sub>WHGL</sub>	Write Recovery before Read		95		ns
t <sub>QVVL</sub>	V <sub>PP</sub> Hold from Valid Status Register (CSR, GSR, BSR) Data and RY/BY # High	3	0		μs
t <sub>WHQV1</sub>	Duration of Word/Byte Write Operation	4,5	5		μs
t <sub>WHQV2</sub>	Duration of Block Erase Operation	4	0.3	10	sec

# 5.8 AC Characteristics for WE #—Controlled Command Write Operations(1)

(Continued)

 $V_{CC} = 5.0V \pm 0.25V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 30 pF

 $V_{CC} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 100 pF

Versions			V <sub>CC</sub> ± 5%		V <sub>CC</sub> ± 10%		Unit
			Min	Max	Min	Max	
Sym	Parameter	Notes					
t <sub>AVAV</sub>	Write Cycle Time		80		85		ns
t <sub>YPWH</sub>	V <sub>pp</sub> Setup to WE # Going High	3	100		100		ns
t <sub>PHL</sub>	RP # Setup to CE # Going Low		480		480		ns
t <sub>ELWL</sub>	CE # Setup to WE # Going Low		0		0		ns
t <sub>AVWH</sub>	Address Setup to WE # Going High	2,6	50		50		ns
t <sub>DVWH</sub>	Data Setup to WE # Going High	2,6	50		50		ns
t <sub>WLWH</sub>	WE # Pulse Width		40		50		ns
t <sub>WHDX</sub>	Data Hold from WE # High	2	0		0		ns
t <sub>WHAX</sub>	Address Hold from WE # High	2	10		10		ns
t <sub>WHEH</sub>	CE # Hold from WE # High		10		10		ns
t <sub>WHWL</sub>	WE # Pulse Width High		30		30		ns
t <sub>GHWL</sub>	Read Recovery before Write		0		0		ns
t <sub>WHRL</sub>	WE # High to RY/BY # Going Low			100		100	ns
t <sub>RHPL</sub>	RP # Hold from Valid Status Register (CSR, GSR, BSR) Data and RY/BY # High	3	0		0		ns
t <sub>PHWL</sub>	RP # High Recovery to WE # Going Low		1		1		μs
t <sub>WHGL</sub>	Write Recovery before Read		60		65		ns
t <sub>QVVL</sub>	V <sub>pp</sub> Hold from Valid Status Register (CSR, GSR, BSR) Data and RY/BY # High	3	0		0		μs
t <sub>WHQV1</sub>	Duration of Word/Byte Write Operation	4,5	4.5		4.5		μs
t <sub>WHQV2</sub>	Duration of Block Erase Operation	4	0.3	10	0.3	10	sec

## NOTES:

CE # is defined as the latter of CE<sub>0</sub> # or CE<sub>1</sub> # going low or the first of CE<sub>0</sub> # or CE<sub>1</sub> # going high.

1. Read timings during write and erase are the same as for normal read.

2. Refer to command definition tables for valid address and data values.

3. Sampled, not 100% tested.

4. Write/Erase durations are measured to valid Status Register (CSR) Data.

5. Word/Byte Write operations are typically performed with 1 Programming Pulse.

6. Address and Data are latched on the rising edge of WE # for all Command Write operations.

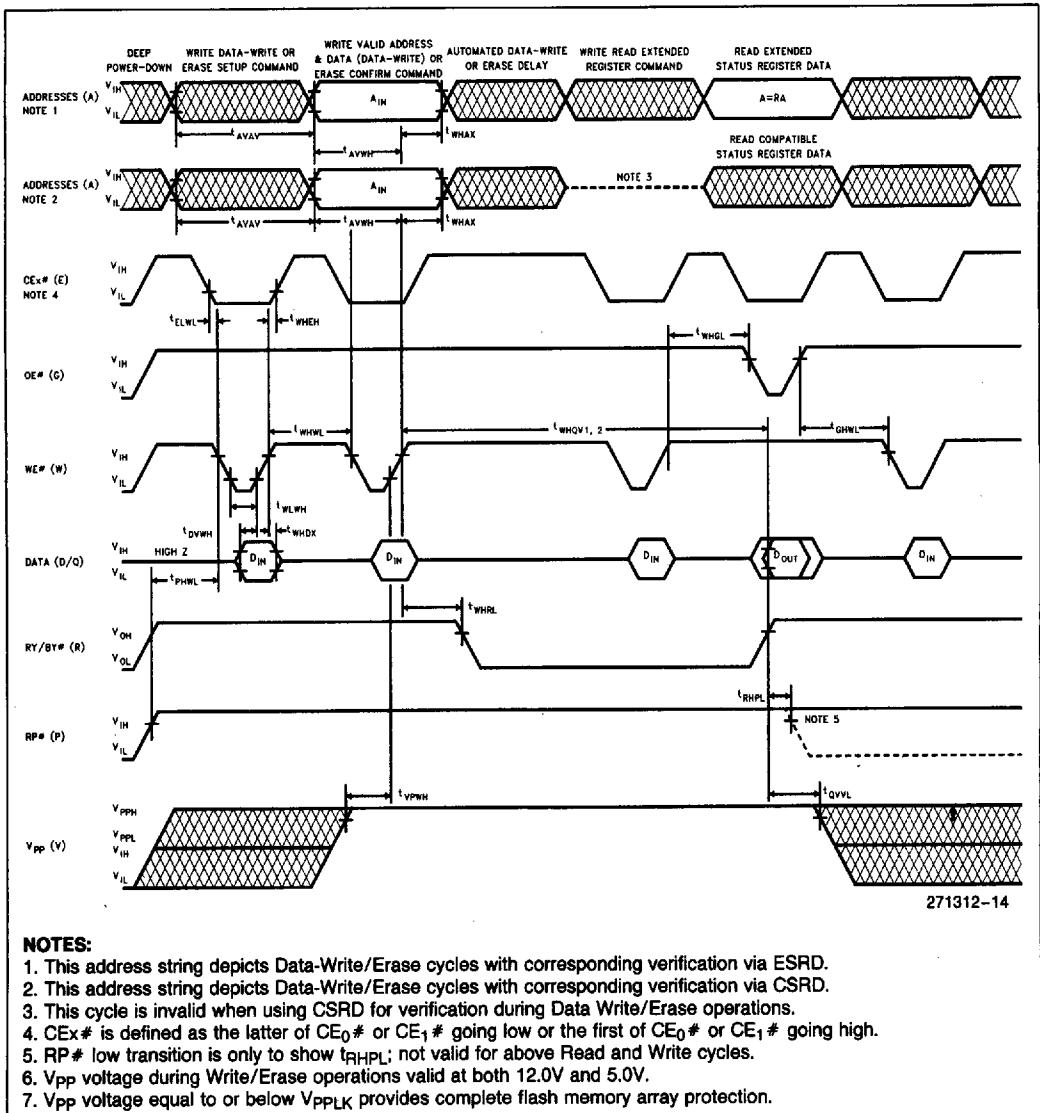


Figure 14. AC Waveforms for Command Write Operations

**5.9 AC Characteristics for CE #—Controlled Command Write Operations<sup>(1)</sup>**
 $V_{CC} = 3.3V \pm 0.3V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 50 pF

Versions					Unit
Sym	Parameter	Notes	Min	Max	
t <sub>AVAV</sub>	Write Cycle Time		120		ns
t <sub>PHWL</sub>	RP # Setup to WE # Going Low		480		ns
t <sub>YPEH</sub>	V <sub>pp</sub> Setup to CE # Going High	3	100		ns
t <sub>WLEL</sub>	WE # Setup to CE # Going Low		0		ns
t <sub>AVEH</sub>	Address Setup to CE # Going High	2,6	75		ns
t <sub>DVEH</sub>	Data Setup to CE # Going High	2,6	75		ns
t <sub>ELEH</sub>	CE # Pulse Width		75		ns
t <sub>EHDx</sub>	Data Hold from CE # High	2	10		ns
t <sub>EHAX</sub>	Address Hold from CE # High	2	10		ns
t <sub>EHWH</sub>	WE hold from CE # High		10		ns
t <sub>EHEL</sub>	CE # Pulse Width High		45		ns
t <sub>GHEL</sub>	Read Recovery before Write		0		ns
t <sub>EHRL</sub>	CE # High to RY/BY # Going Low			100	ns
t <sub>RHPL</sub>	RP # Hold from Valid Status Register (CSR, GSR, BSR) Data and RY/BY # High	3	0		ns
t <sub>PHL</sub>	RP # High Recovery to CE # Going Low		480		ns
t <sub>EHGL</sub>	Write Recovery before Read		95		ns
t <sub>QVVL</sub>	V <sub>pp</sub> Hold from Valid Status Register (CSR, GSR, BSR) Data and RY/BY # High		0		μs
t <sub>EHQV1</sub>	Duration of Word/Byte Write Operation	4,5	5		μs
t <sub>EHQV2</sub>	Duration of Block Erase Operation	4	0.3	10	sec



**5.9 AC Characteristics for CE#—Controlled Command Write Operations<sup>(1)</sup>**

(Continued)

$V_{CC} = 5.0V \pm 0.25V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 30 pF  
 $V_{CC} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 100 pF

Versions <sup>(4)</sup>			$V_{CC} \pm 5\%$		$V_{CC} \pm 10\%$		Unit
			Min	Max	Min	Max	
Sym	Parameter	Notes	Min	Max	Min	Max	
$t_{AVAV}$	Write Cycle Time		80		85		ns
$t_{PHWL}$	RP# Setup to WE# Going Low	3	480		480		ns
$t_{VPEH}$	$V_{PP}$ Setup to CE# Going High	3	100		100		ns
$t_{WLEL}$	WE# Setup to CE# Going Low		0		0		ns
$t_{AVEH}$	Address Setup to CE# Going High	2,6	50		50		ns
$t_{DVEH}$	Data Setup to CE# Going High	2,6	50		50		ns
$t_{ELEH}$	CE# Pulse Width		40		50		ns
$t_{EHDX}$	Data Hold from CE# High	2	0		0		ns
$t_{EHAX}$	Address Hold from CE# High	2	10		10		ns
$t_{EHWL}$	WE Hold from CE# High		10		10		ns
$t_{EHEL}$	CE# Pulse Width High		30		30		ns
$t_{GHLE}$	Read Recovery before Write		0		0		ns
$t_{EHRL}$	CE# High to RY/BY# Going Low			100		100	ns
$t_{RHPL}$	RP# Hold from Valid Status Register (CSR, GSR, BSR) Data and RY/BY# High	3	0		0		ns
$t_{PHEL}$	RP# High Recovery to CE# Going Low		1		1		$\mu s$
$t_{EHGL}$	Write Recovery before Read		60		65		ns
$t_{QVVL}$	$V_{PP}$ Hold from Valid Status Register (CSR, GSR, BSR) Data at RY/BY# High		0		0		$\mu s$
$t_{EHQV1}$	Duration of Word/Byte Write Operation	4,5	4.5		4.5		$\mu s$
$t_{EHQV2}$	Duration of Block Erase Operation	4	0.3	10	0.3	10	sec

**NOTES:**

CE# is defined as the latter of CE<sub>0</sub># or CE<sub>1</sub># going low or the first of CE<sub>0</sub># or CE<sub>1</sub># going high.

1. Read timings during write and erase are the same as for normal read.

2. Refer to command definition tables for valid address and data values.

3. Sampled, not 100% tested.

4. Write/Erase durations are measured to valid Status Data.

5. Word/Byte Write operations are typically performed with 1 Programming Pulse.

6. Address and Data are latched on the rising edge of CE# for all Command Write Operations.

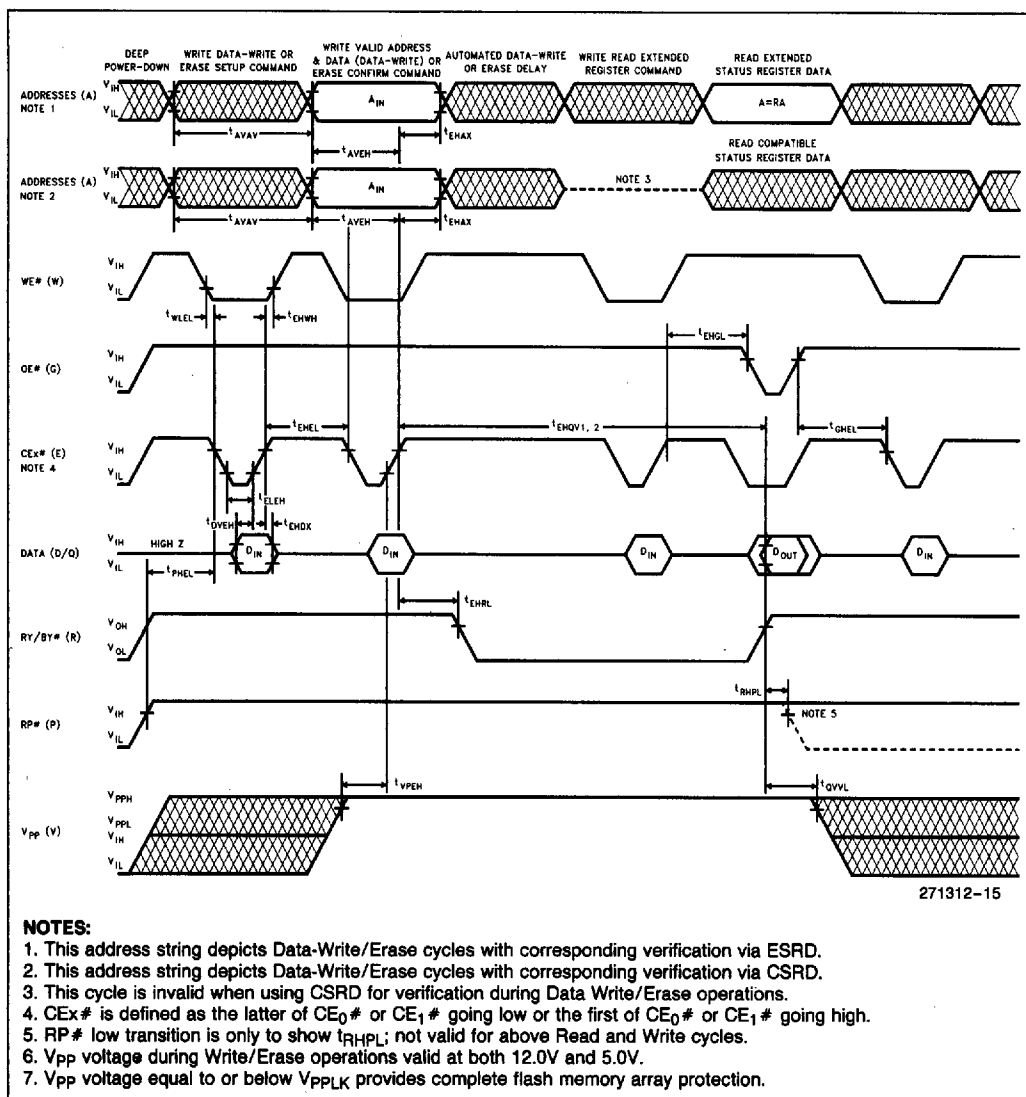


Figure 15. Alternate AC Waveforms for Command Write Operations

### 5.10 AC Characteristics for WE #—Controlled Page Buffer Write Operations<sup>(1)</sup>

$V_{CC} = 3.3V \pm 0.3V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 50 pF

Versions			28F016SV-120			Unit
Sym	Parameter	Notes	Min	Typ	Max	
$t_{AVWL}$	Address Setup to WE# Going Low	2	25			ns

$V_{CC} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 50 pF

Versions <sup>(3)</sup>		V <sub>CC</sub> ± 5%	28F016SV-080 <sup>(4)</sup>						Unit
		V <sub>CC</sub> ± 10%	28F016SV-080 <sup>(5)</sup>			28F016SV-085 <sup>(5)</sup>			
Sym	Parameter	Notes	Min	Typ	Max	Min	Typ	Max	
t <sub>AVWL</sub>	Address Setup to WE# Going Low	2	15			15			ns

#### NOTES:

1. All other specifications for WE #—Controlled Write Operations can be found in section 5.8.
2. Address must be valid during the entire WE# low pulse.
3. Device speeds are defined as:  
80/85 ns at  $V_{CC} = 5.0V$  equivalent to  
120 ns at  $V_{CC} = 3.3V$
4. See the high speed AC Input/Output Reference Waveforms and AC Testing Load Circuit.
5. See the standard AC Input/Output Reference Waveforms and AC Testing Load Circuit.

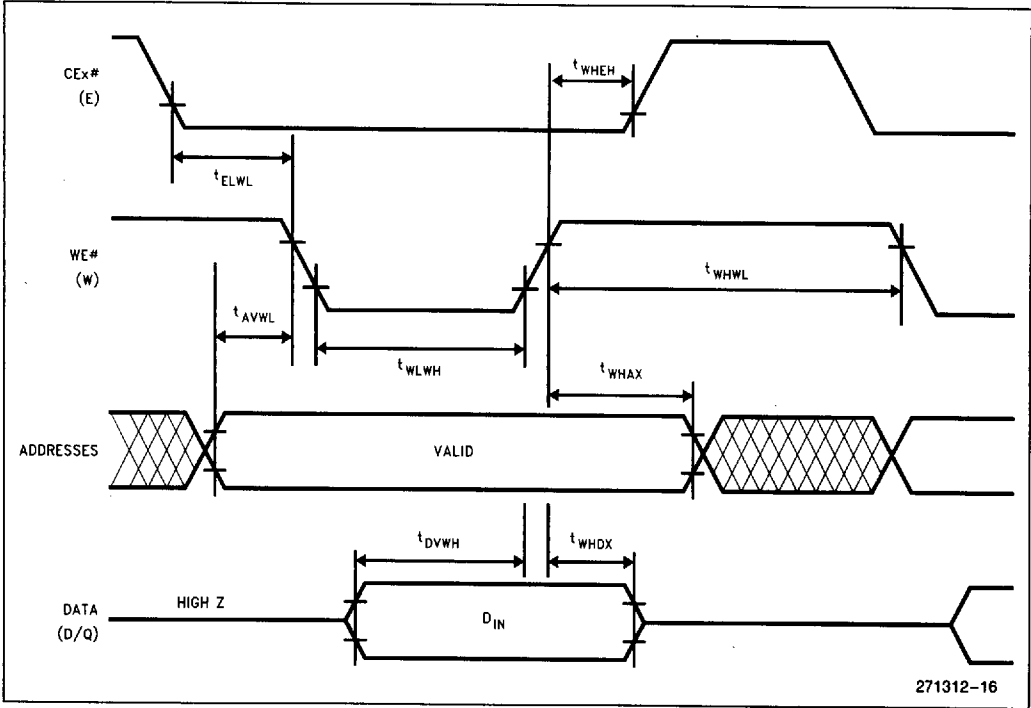


Figure 16. Page Buffer Write Timing Waveforms

# 5.11 AC Characteristics for CE#—Controlled Page Buffer Write Operations(1)

$V_{CC} = 3.3V \pm 0.3V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 50 pF

Versions			28F016SV-120			Unit
Sym	Parameter	Notes	Min	Typ	Max	
$t_{A\overline{V}EL}$	Address Setup to CE# Going Low	2, 3	25			ns

$V_{CC} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ , Load = 50 pF

Versions(4)		V <sub>CC</sub> ± 5%	28F016SV-080(5)						Unit
		V <sub>CC</sub> ± 10%	28F016SV-080(6)			28F016SV-085(6)			
Sym	Parameter	Notes	Min	Typ	Max	Min	Typ	Max	
t <sub>AVEL</sub>	Address Setup to CE# Going Low	2, 3	15			15			ns

## NOTES:

1. All other specifications for CE#—Controlled Write Operations can be found in section 5.9.
2. Address must be valid during the entire CE# low pulse.
3. CE# is defined as the latter of CE<sub>0</sub># or CE<sub>1</sub># going low, or the first of CE<sub>0</sub># or CE<sub>1</sub># going high.
4. Device speeds are defined as:  
80/85 ns at  $V_{CC} = 5.0V$  equivalent to  
120 ns at  $V_{CC} = 3.3V$
5. See the high speed AC Input/Output Reference Waveforms and AC Testing Load Circuit.
6. See the standard AC Input/Output Reference Waveforms and AC Testing Load Circuit.

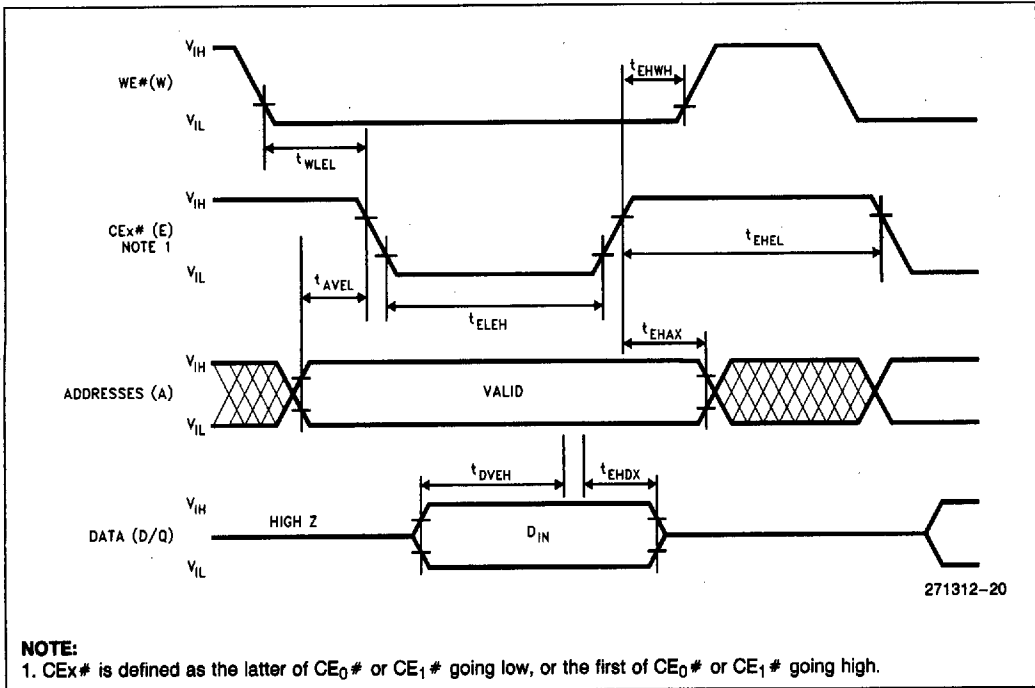


Figure 17. Controller Page Buffer Write Timing Waveforms  
(Loading Data to the Page Buffer)

**5.12 Erase and Word/Byte Write Performance(1,3)** $V_{CC} = 3.3V \pm 0.3V$ ,  $V_{PP} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ 

Sym	Parameter	Notes	Min	Typ(1)	Max	Units	Test Conditions
	Page Buffer Byte Write Time	2		8.0		$\mu s$	
	Page Buffer Word Write Time	2		16		$\mu s$	
	Byte Write Time	2		29		$\mu s$	
	Word Write Time	2		35		$\mu s$	
$t_{WHRH2}$	Block Write Time	2		1.9		sec	Byte Write Mode
$t_{WHRH3}$	Block Write Time	2		1.2		sec	Word Write Mode
	Block Erase Time	2		2.5		sec	
	Full Chip Erase Time	2		80		sec	

 $V_{CC} = 3.3V \pm 0.3V$ ,  $V_{PP} = 12.0V \pm 0.6V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$ 

Sym	Parameter	Notes	Min	Typ(1)	Max	Units	Test Conditions
	Page Buffer Byte Write Time	2		2.2		$\mu s$	
	Page Buffer Word Write Time	2		4.4		$\mu s$	
$t_{WHRH1}$	Word/Byte Write Time	2		9		$\mu s$	
$t_{WHRH2}$	Block Write Time	2		0.6	2.1	sec	Byte Write Mode
$t_{WHRH3}$	Block Write Time	2		0.3	1.0	sec	Word Write Mode
	Block Erase Time	2		1.8	10	sec	
	Full Chip Erase Time	2		48		sec	



### 5.12 Erase and Word/Byte Write Performance<sup>(1,3)</sup> (Continued)

$V_{CC} = 5.0V$ ,  $V_{PP} = 5.0V \pm 0.5V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$

Sym	Parameter	Notes	Min	Typ(1)	Max	Units	Test Conditions
	Page Buffer Byte Write Time	2		8		$\mu s$	
	Page Buffer Word Write Time	2		16		$\mu s$	
	Byte Write Time	2		20		$\mu s$	
	Word Write Time	2		25		$\mu s$	
$t_{WHRH2}$	Block Write Time	2		1.4		sec	Byte Write Mode
$t_{WHRH3}$	Block Write Time	2		0.85		sec	Word Write Mode
	Block Erase Time	2		2		sec	
	Full Chip Erase Time	2		64		sec	

$V_{CC} = 5.0V$ ,  $V_{PP} = 12.0V \pm 0.6V$ ,  $T_{ASE2} = -40^{\circ}C$  to  $+125^{\circ}C$ ,  $T_{ASE1} = -55^{\circ}C$  to  $+125^{\circ}C$

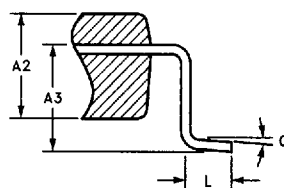
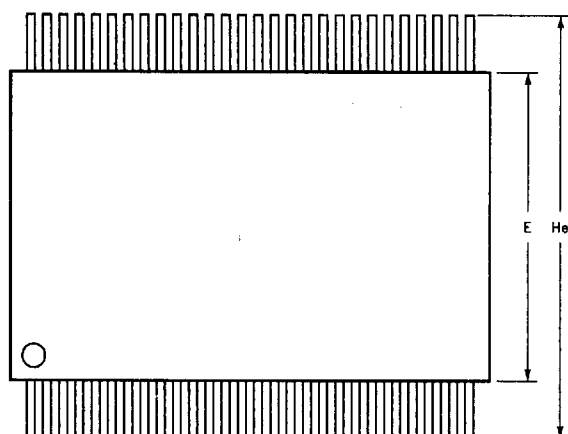
Sym	Parameter	Notes	Min	Typ(1)	Max	Units	Test Conditions
	Page Buffer Byte Write Time	2		2.1		$\mu s$	
	Page Buffer Word Write Time	2		4.1		$\mu s$	
$t_{WHRH1}$	Word Byte/Write Time	2		6		$\mu s$	
$t_{WHRH2}$	Block Write Time	2		0.4	2.1	sec	Byte Write Mode
$t_{WHRH3}$	Block Write Time	2		0.2	1.0	sec	Word Write Mode
	Block Erase Time	2		1.8	10	sec	
	Full Chip Erase Time	2		48		sec	

**NOTES:**

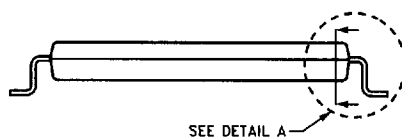
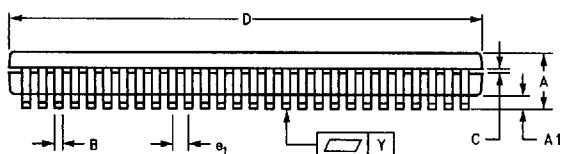
1. 25°C, and normal voltages.
2. Excludes system-level overhead.
3. These performance numbers are valid for all speed versions.

## 6.0 MECHANICAL SPECIFICATIONS

56-Lead Shrink Small Outline Package (SSOP)



DETAIL A



SEE DETAIL A

271312-17

COPPER ALLOY 194									
Control Dimensions in Millimeters	Symbol	Millimeters			Notes	Inches			Notes
		Min	Nom	Max		Min	Nom	Max	
Package Height	A		1.80	1.90			0.070	0.075	
Standoff	A1	0.47				0.018			
Package Body Thickness	A2	1.18	1.28	1.38		0.046	0.050	0.054	
Lead Width	B	0.25	0.30	0.40		0.010	0.012	0.016	
Lead Thickness	C	0.13	0.15	0.20		0.005	0.006	0.008	
Package Body Length	D	23.40	23.70	24.00		0.921	0.933	0.945	
Package Body Width	E	13.10	13.30	13.50		0.516	0.524	0.531	
Pitch	e1		0.80				0.0315		
Terminal Dimension	He	15.70	16.00	16.30		0.618	0.630	0.642	
Lead Count	N		56				56		
Lead Tip Length	L	0.75	0.80	0.85		0.030	0.031	0.033	
Seating Plane Coplanarity	Y			0.10				0.004	
Lead Height	A3	1.30	1.40	1.50		0.051	0.055	0.059	
Lead Tip Angle	Q			5				5	





DEVICE NOMENCLATURE

V	S	2	8	F	0	1	6	S	V	—	8	5
M	S	2	8	F	0	1	6	S	V	—	8	5

V = SE2  
M = SE1

S = SSOP

SV = SmartVoltage Technology

Access Speed

Depending on system design specifications, the VS/MS28F016SV-70 is capable of supporting

- 80 ns access times with a V<sub>CC</sub> of 5.0V ±5% and loading of 30 pF
- 85 ns access times with a V<sub>CC</sub> of 5.0V ±10% and loading of 100 pF
- 120 ns access times with a V<sub>CC</sub> of 3.3V ±10% and loading of 50 pF

ADDITIONAL INFORMATION

	Item	Order Number
AP 393	28F016SV Compatibility with 28F016SA	292144
	28F016SA User's Manual	297372
AP 377	28F016SA Software Drivers	292126
AP 378	System Optimization Using the Enhanced Features of the 28F016SA	292127
AP 375	Upgrade Considerations from the 28F008SA to the 28F016SA	292124
ER 33	ETOX™ Flash Memory Technology—Insight to Intel's Fourth Generation Process Innovation	294016
	VE28F008 or M28F008 Data Sheet	271305
	M28F008 Datasheet	271232

Please check with Intel Literature for availability.

DATA SHEET REVISION HISTORY

Number	Description
001	Original Version